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(54) **SEMICONDUCTOR DEVICE, PHOTONIC
CIRCUIT AND METHOD FOR ADJUSTING
RESONANT WAVELENGTH OF OPTICAL
MODULATOR**

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(57) **ABSTRACT**

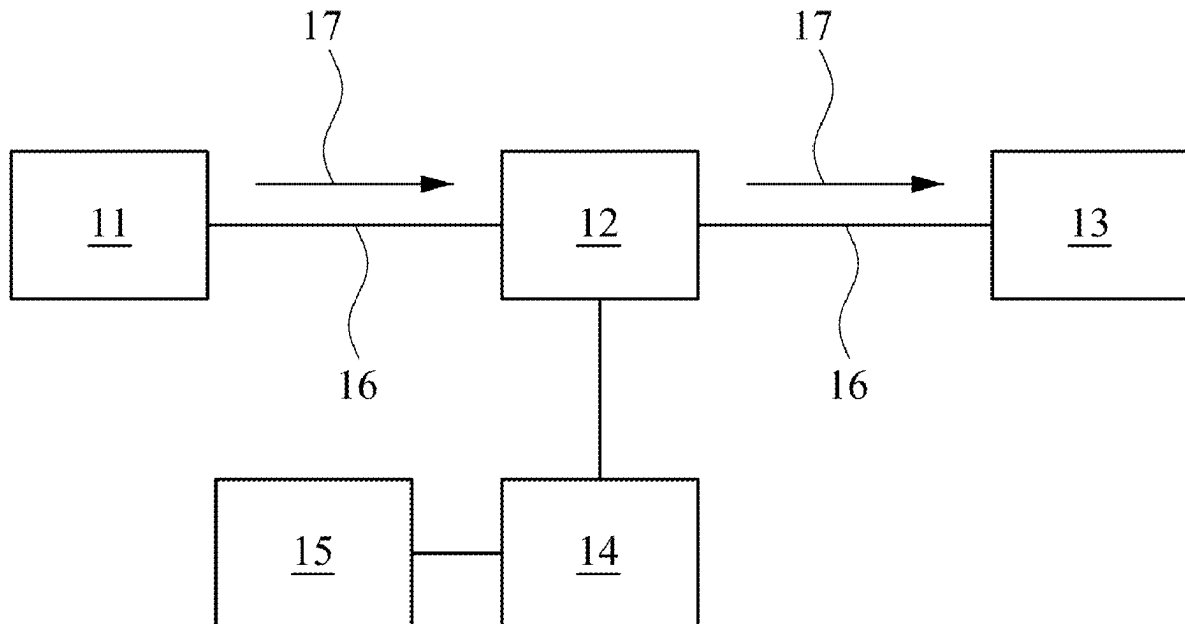
The present disclosure provides semiconductor devices and photonic circuits. The semiconductor device includes a substrate and an optical modulator disposed on the substrate. The optical modulator includes a first PIN portion and a second PIN portion apart from the first PIN portion. The optical modulator is configured to receive a voltage from a driver to decrease a resonant wavelength of the optical modulator.

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(22) Filed: **Apr. 29, 2025**

Related U.S. Application Data

(63) Continuation of application No. 18/599,189, filed on
Mar. 7, 2024, now Pat. No. 12,313,879, which is a



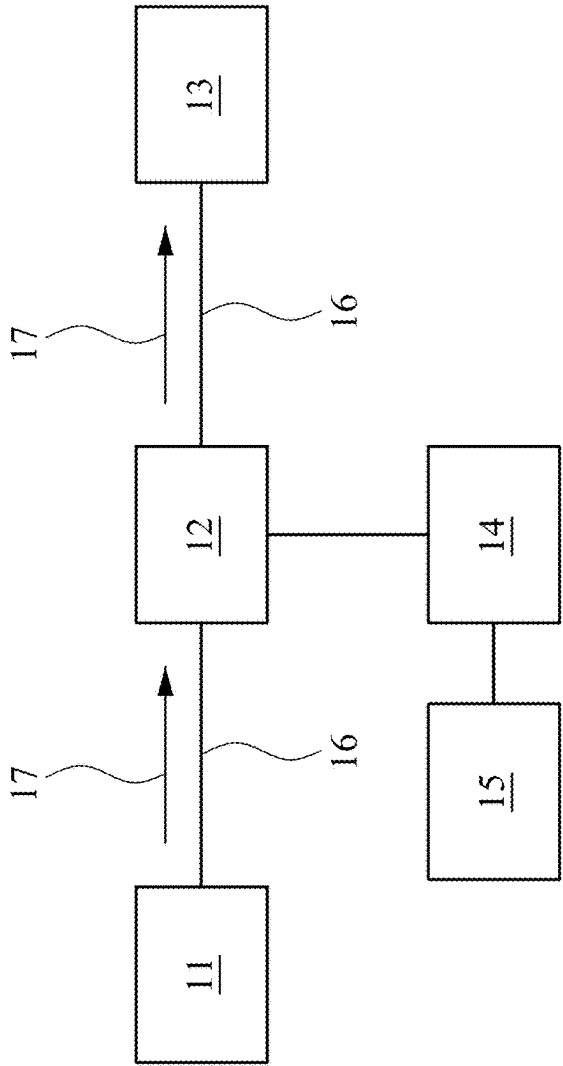


FIG. 1A

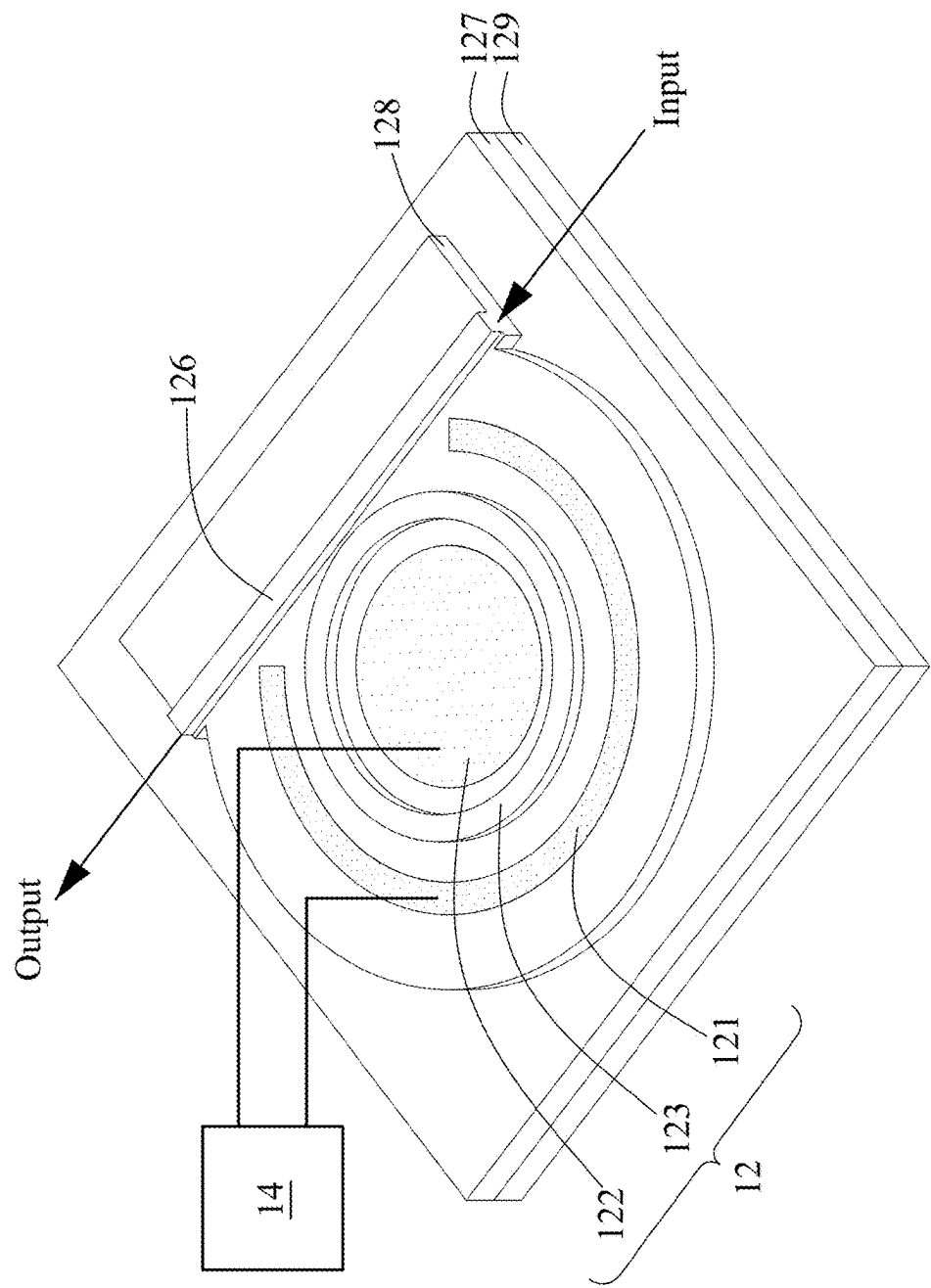


FIG. 1B

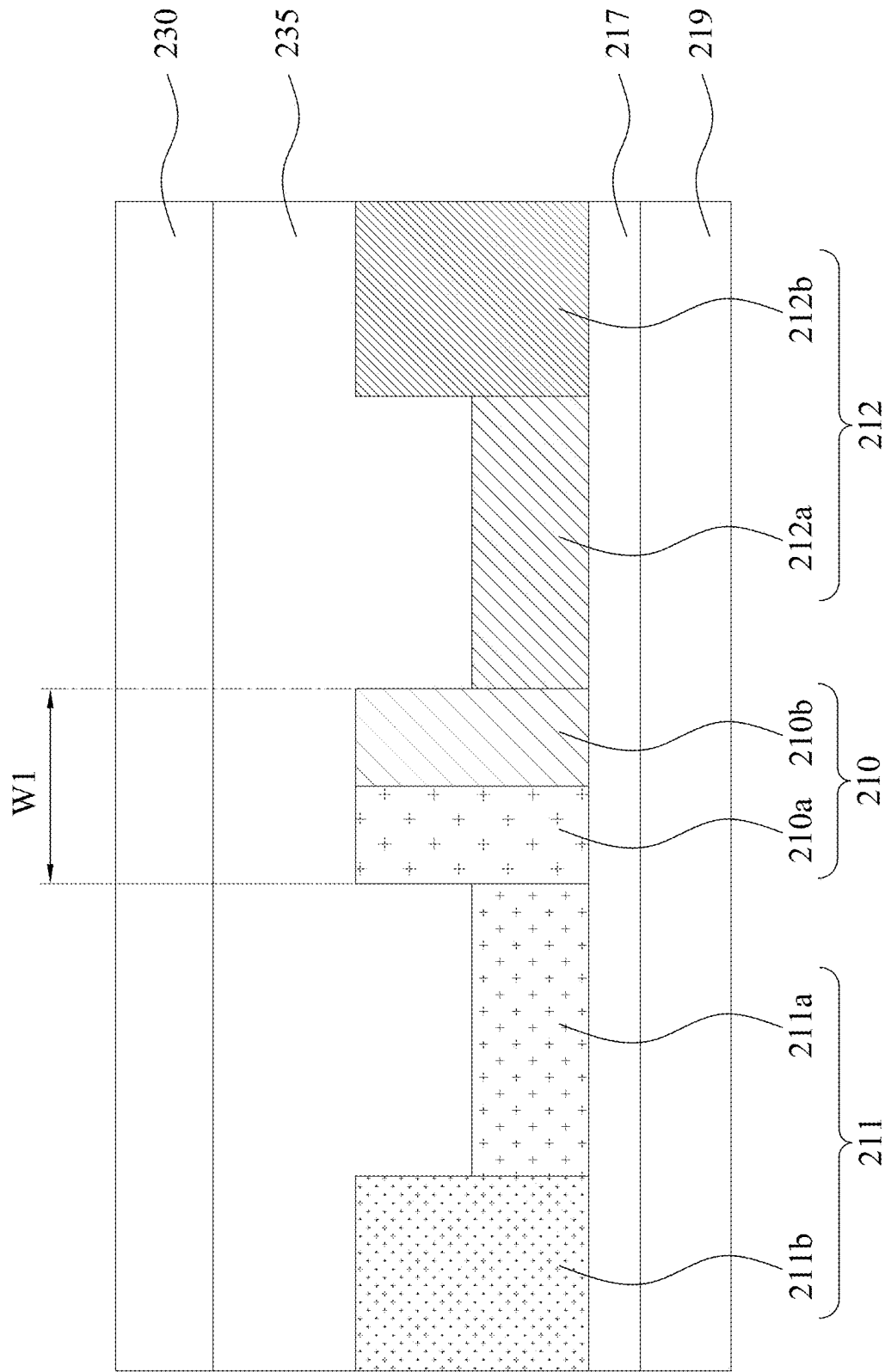


FIG. 2B

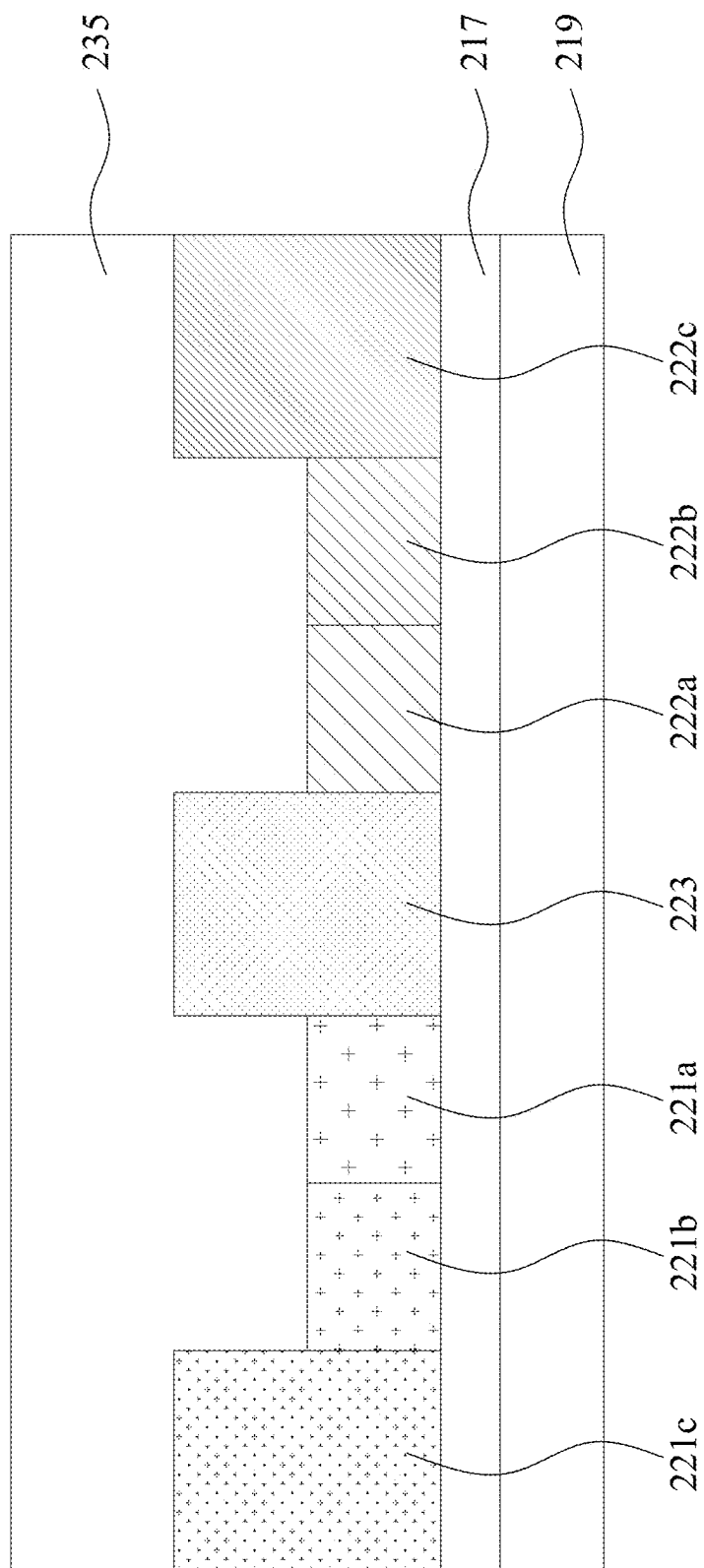


FIG. 2C

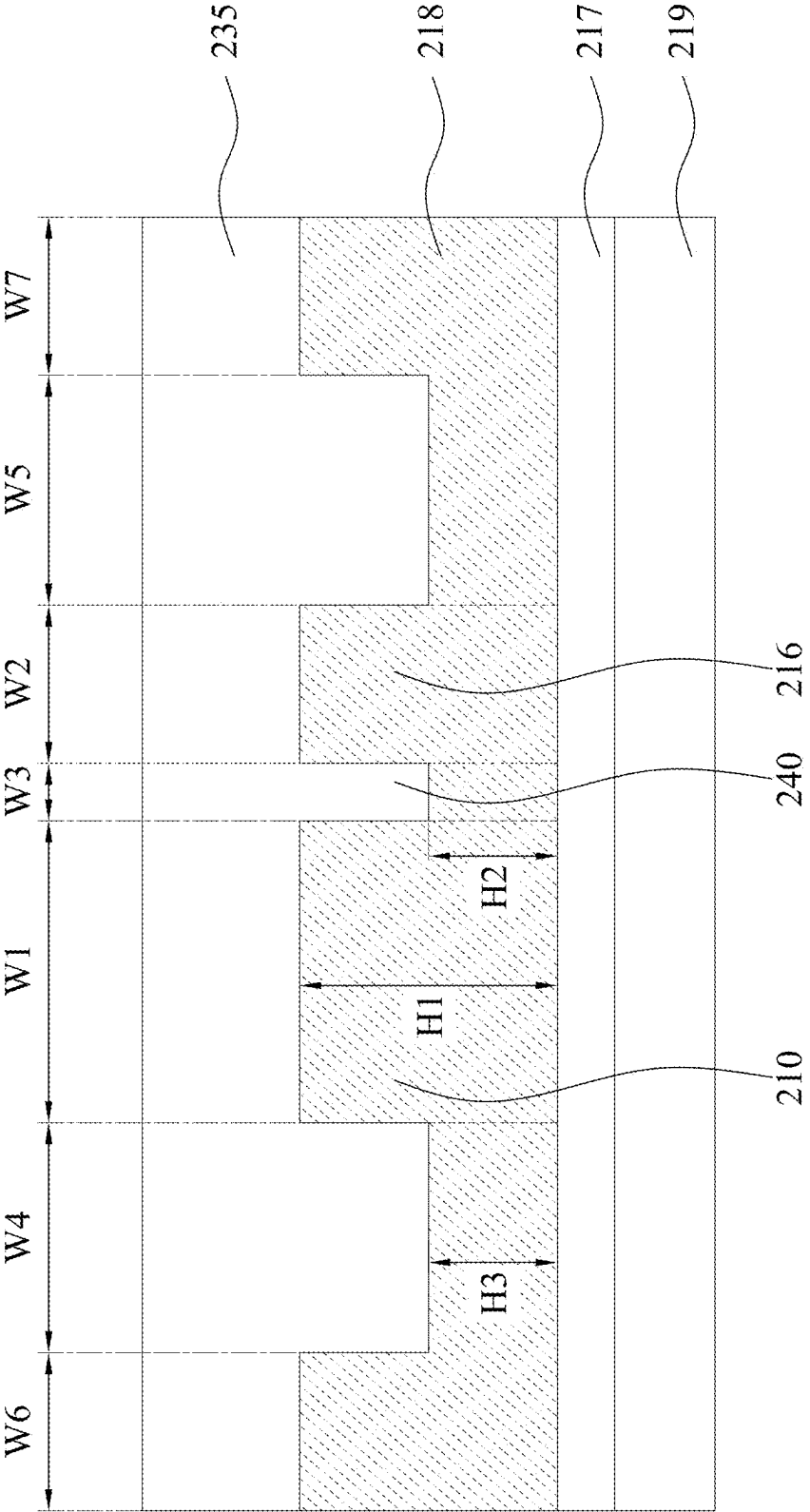


FIG. 2D

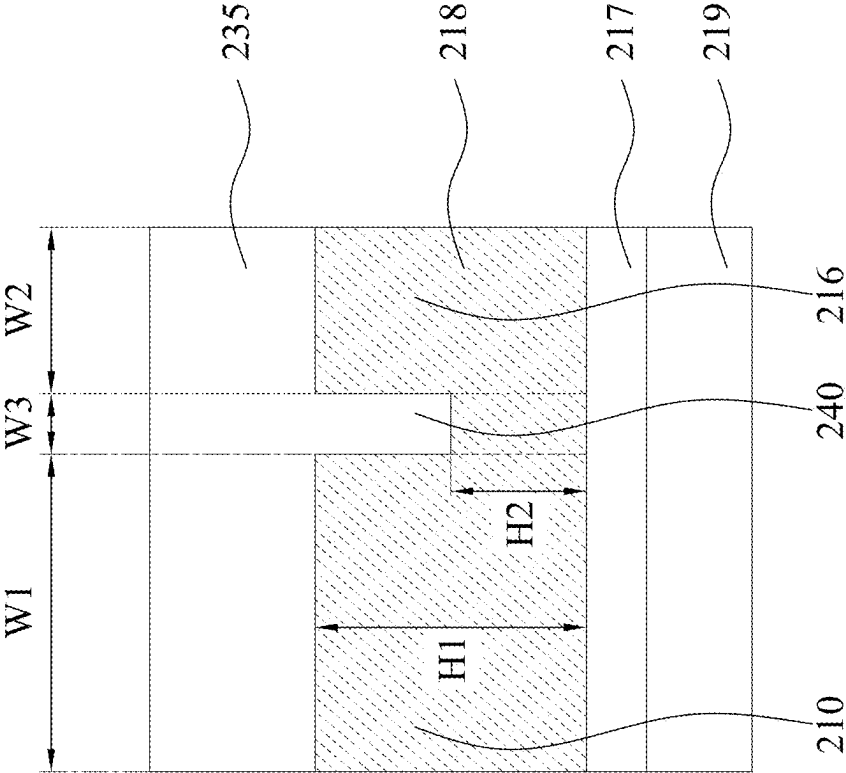


FIG. 2E

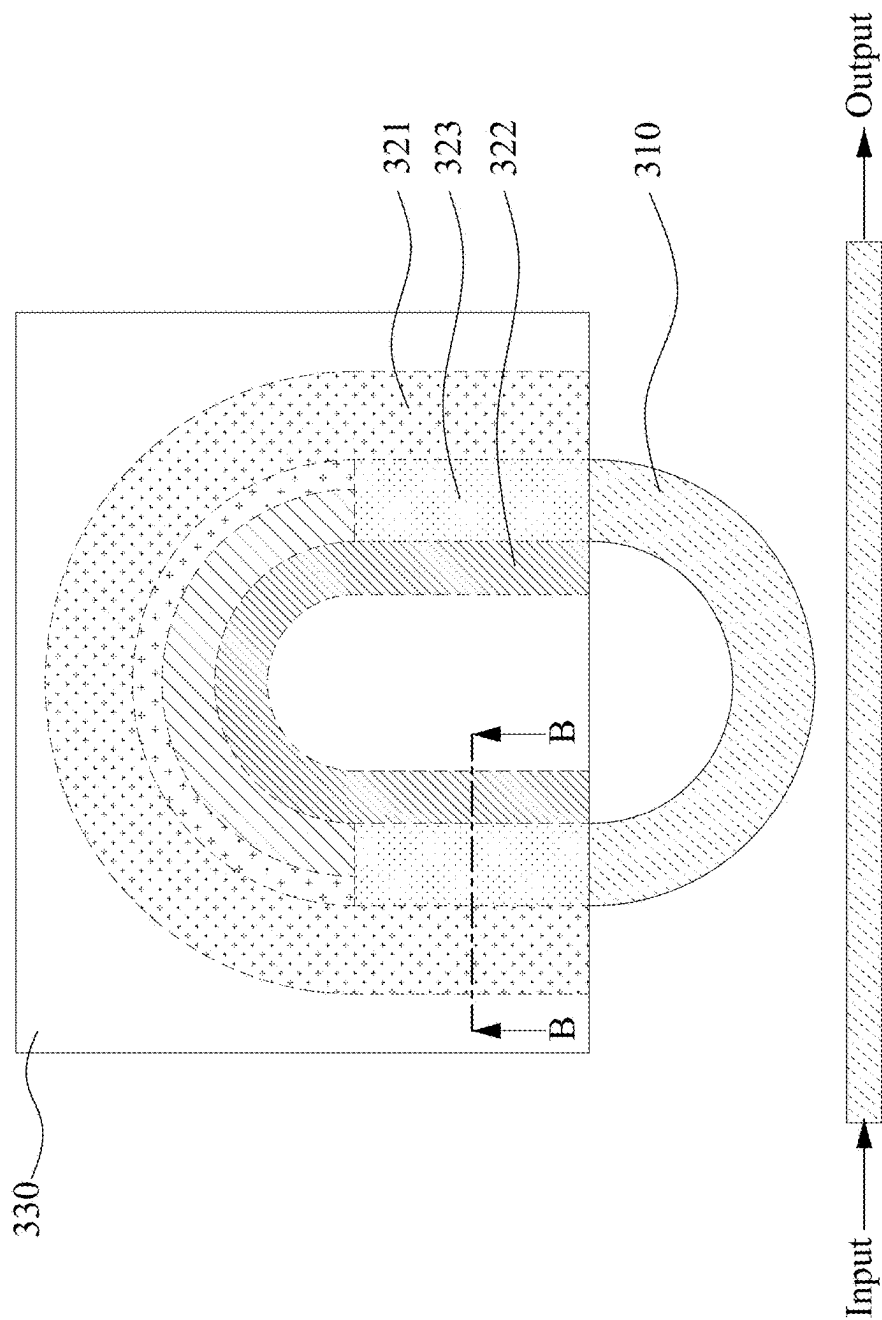


FIG. 3A

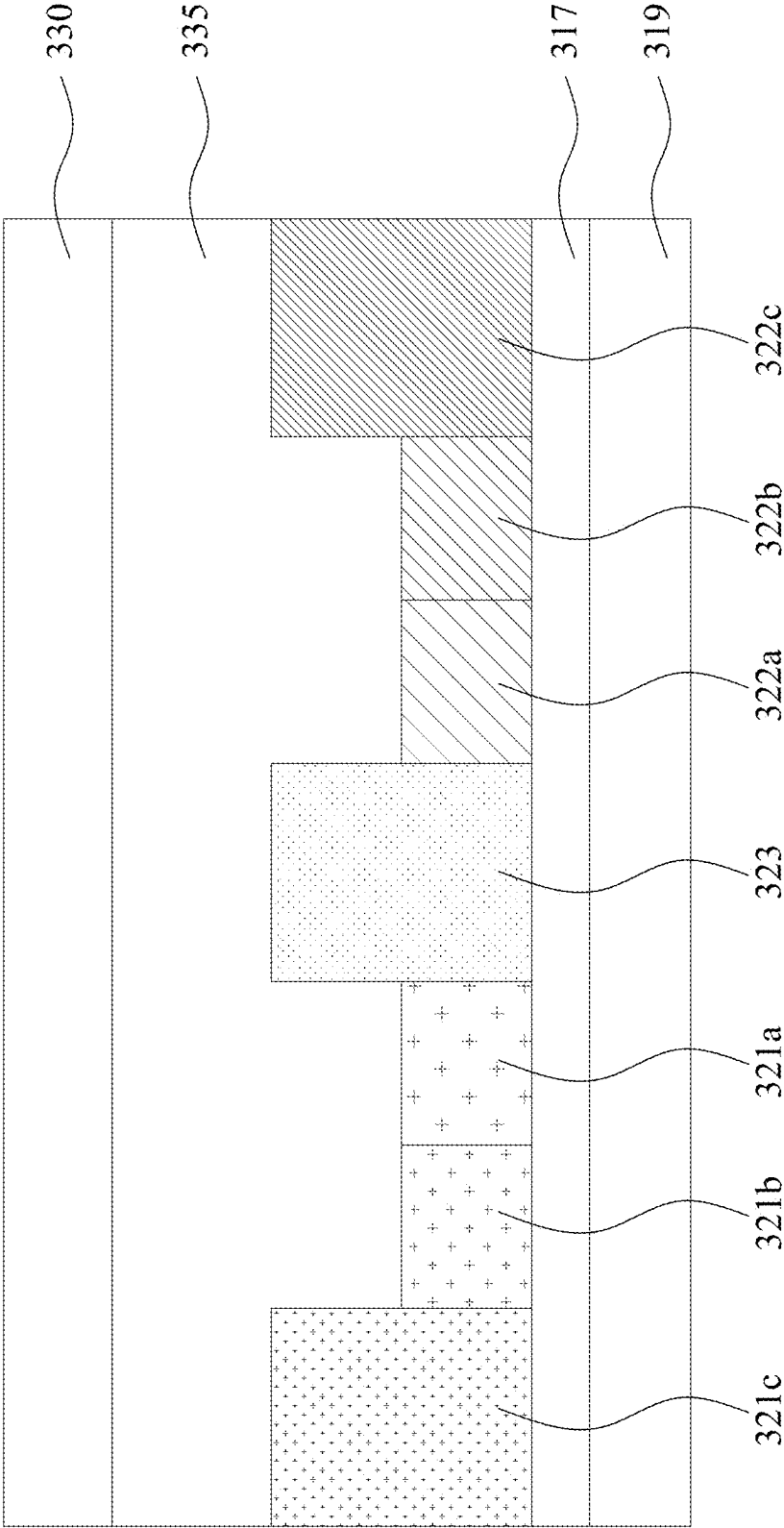


FIG. 3B

12C

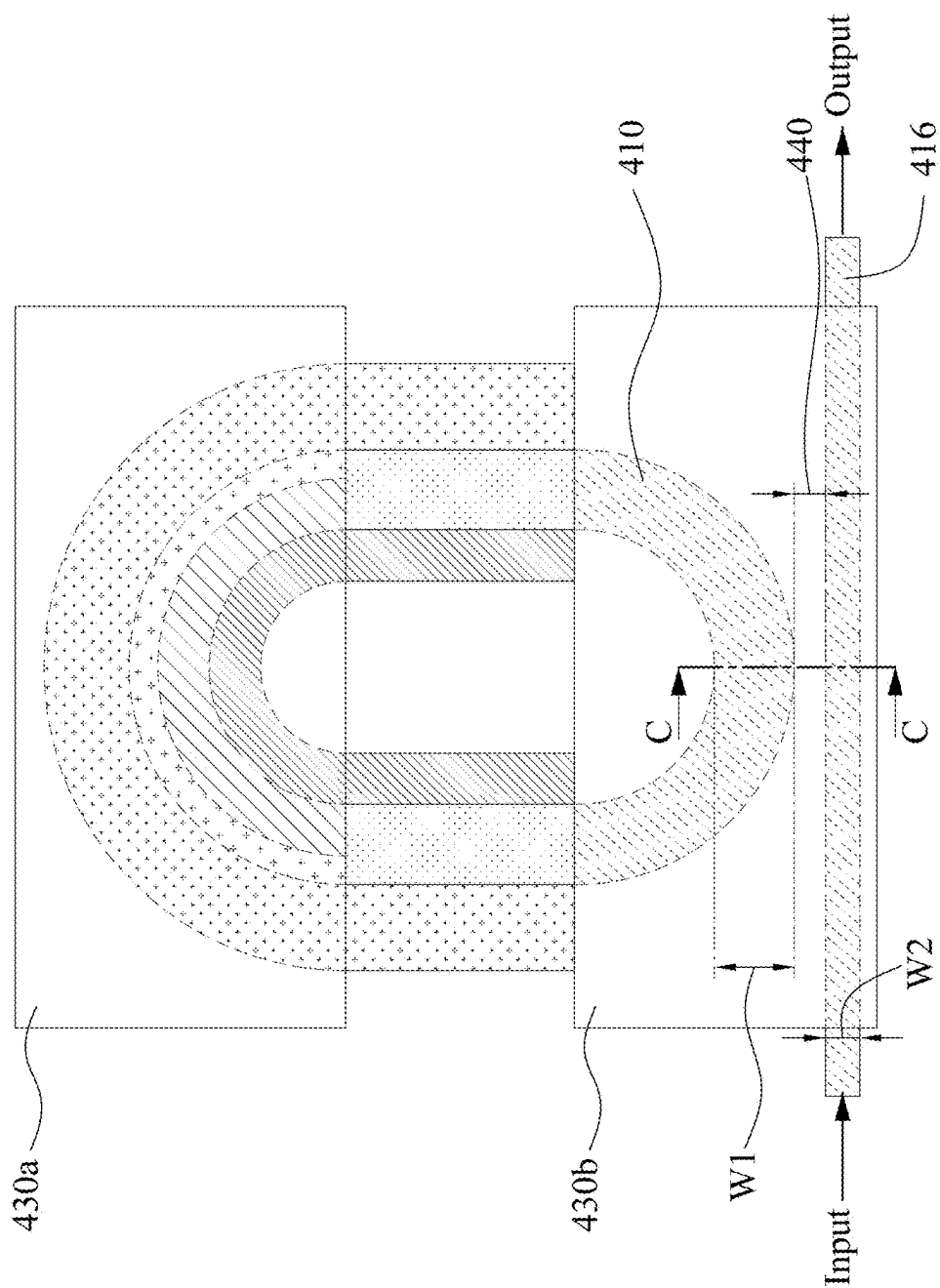


FIG. 4A

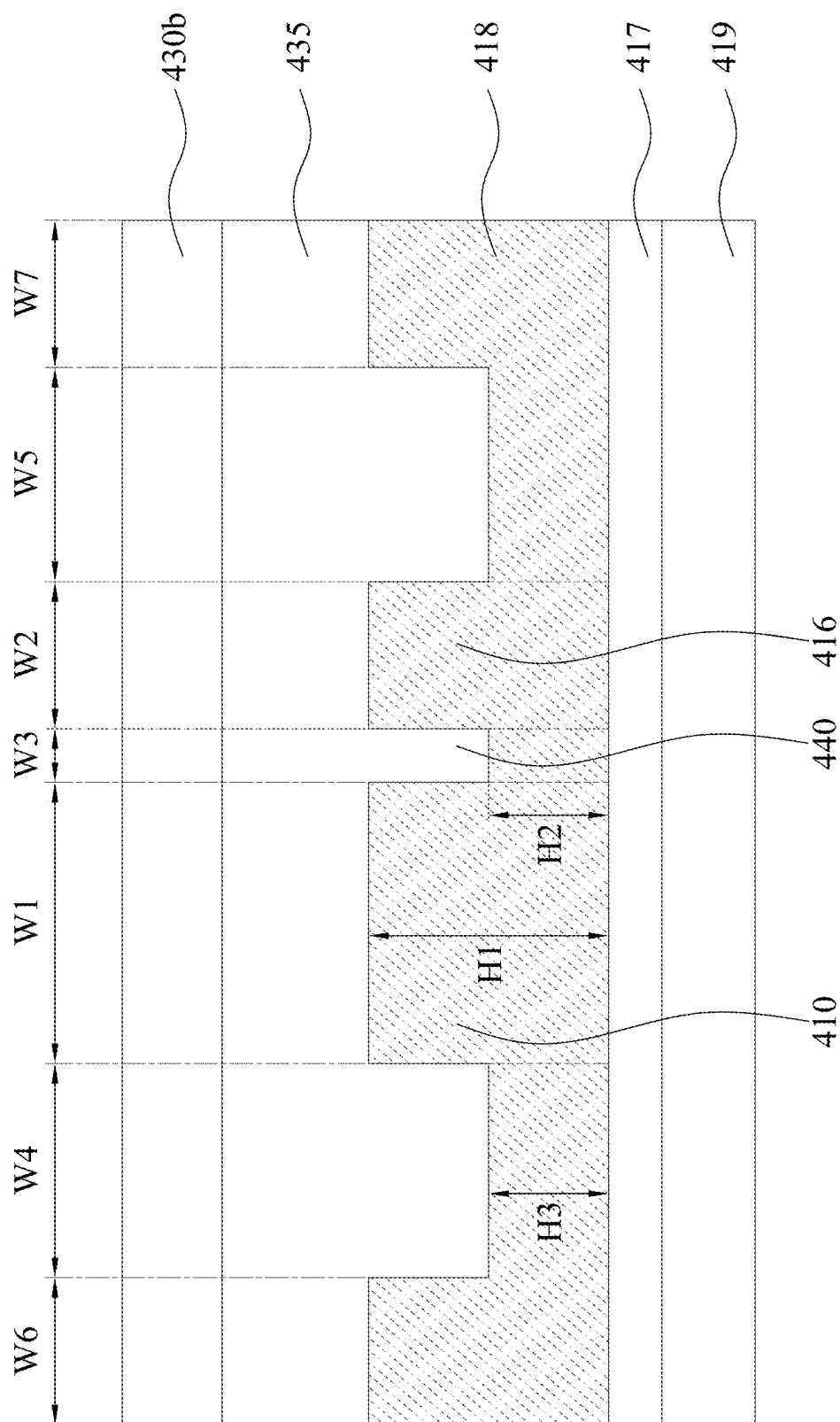


FIG. 4B

12D

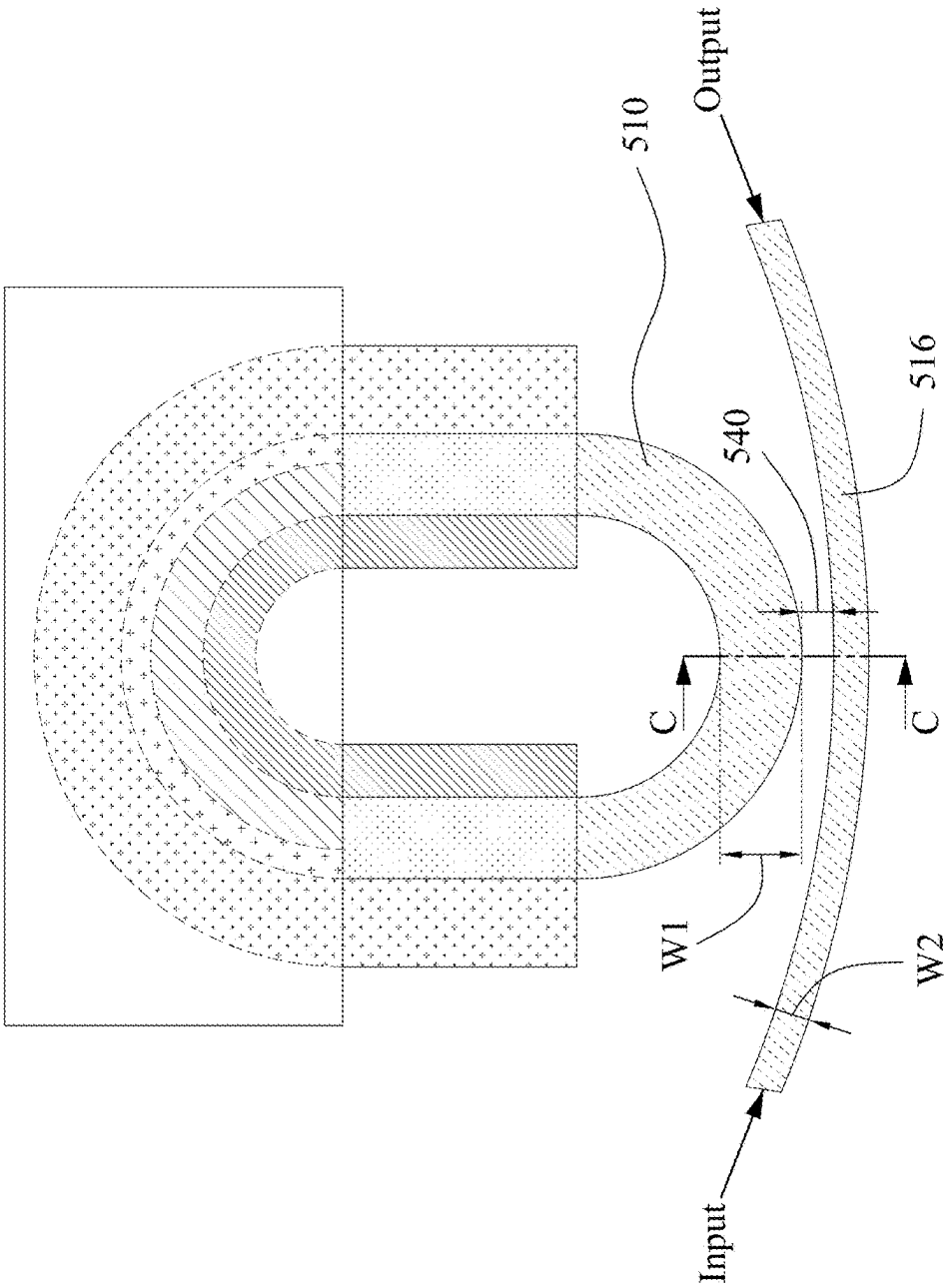


FIG. 5A

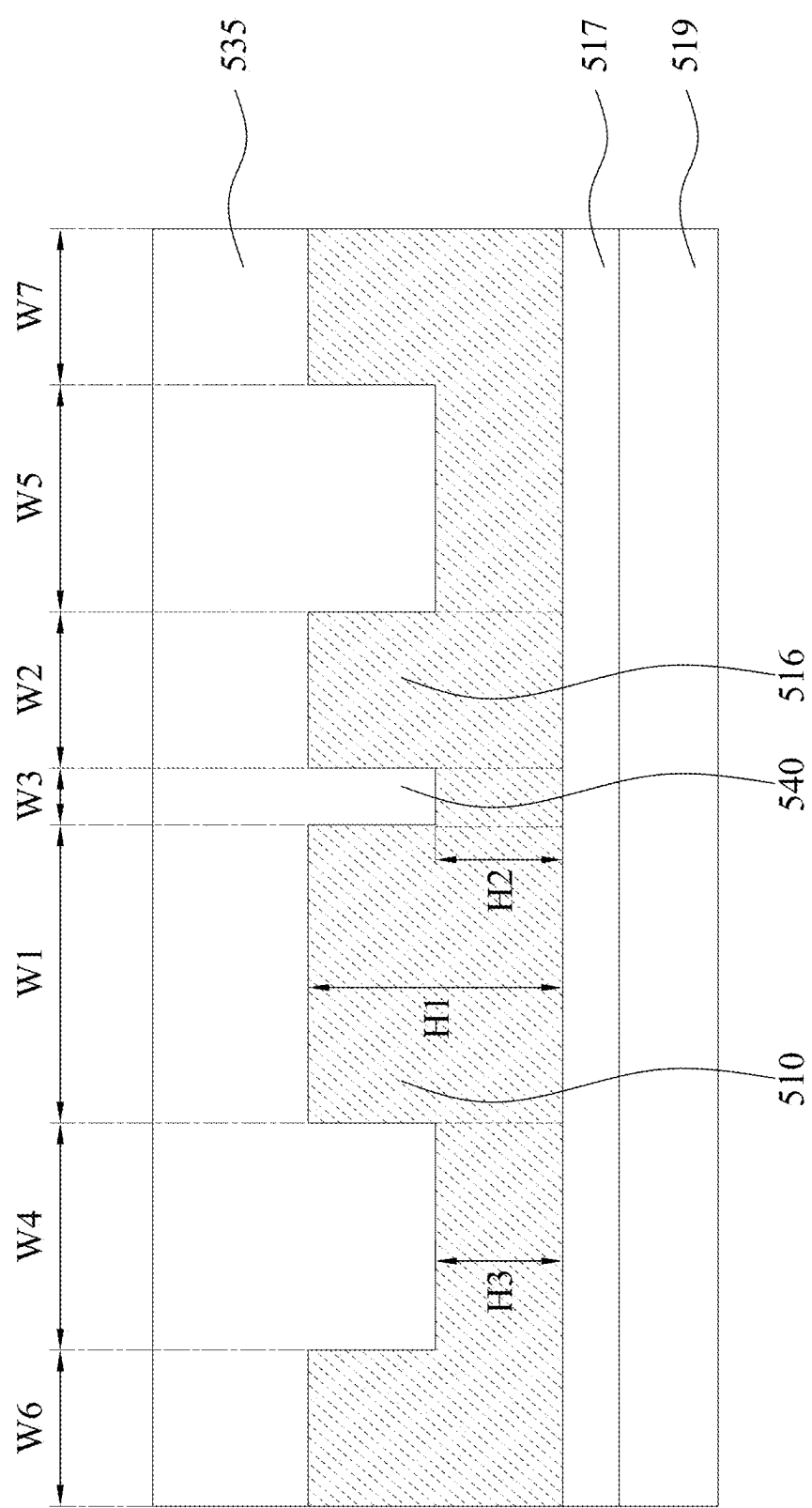


FIG. 5B

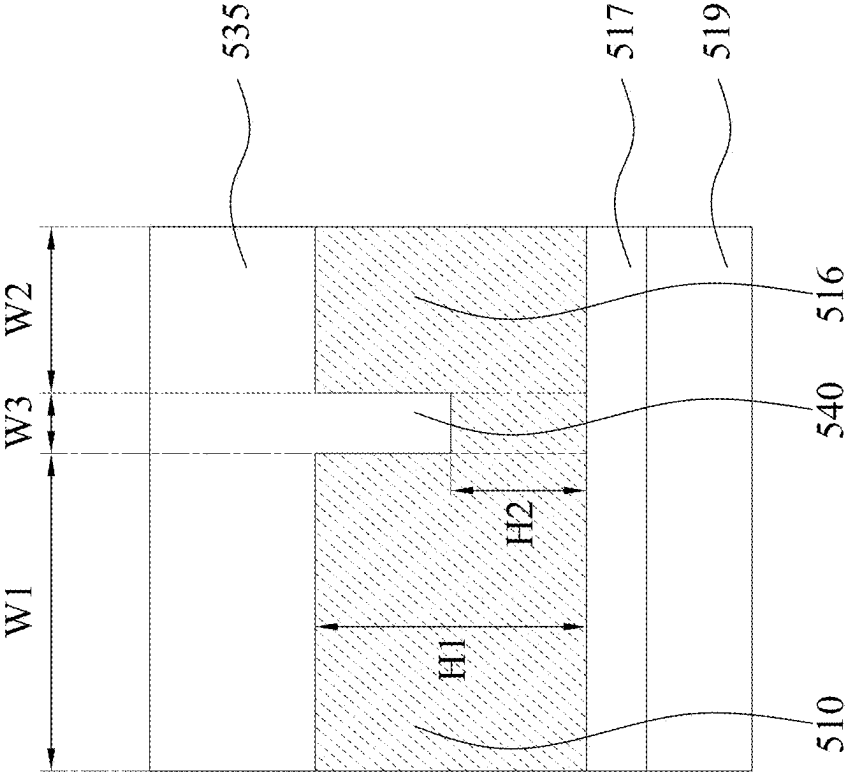


FIG. 5C

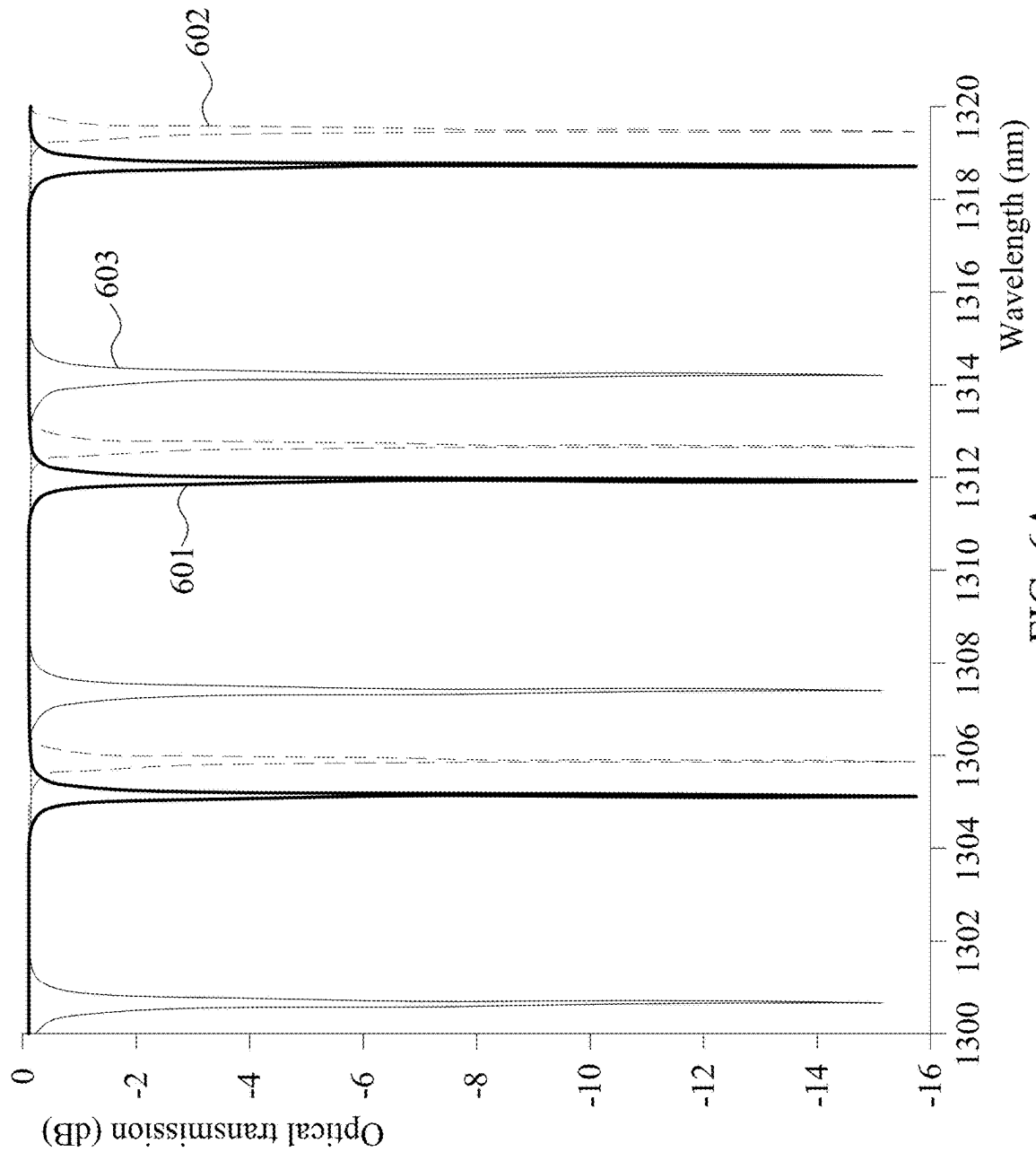


FIG. 6A

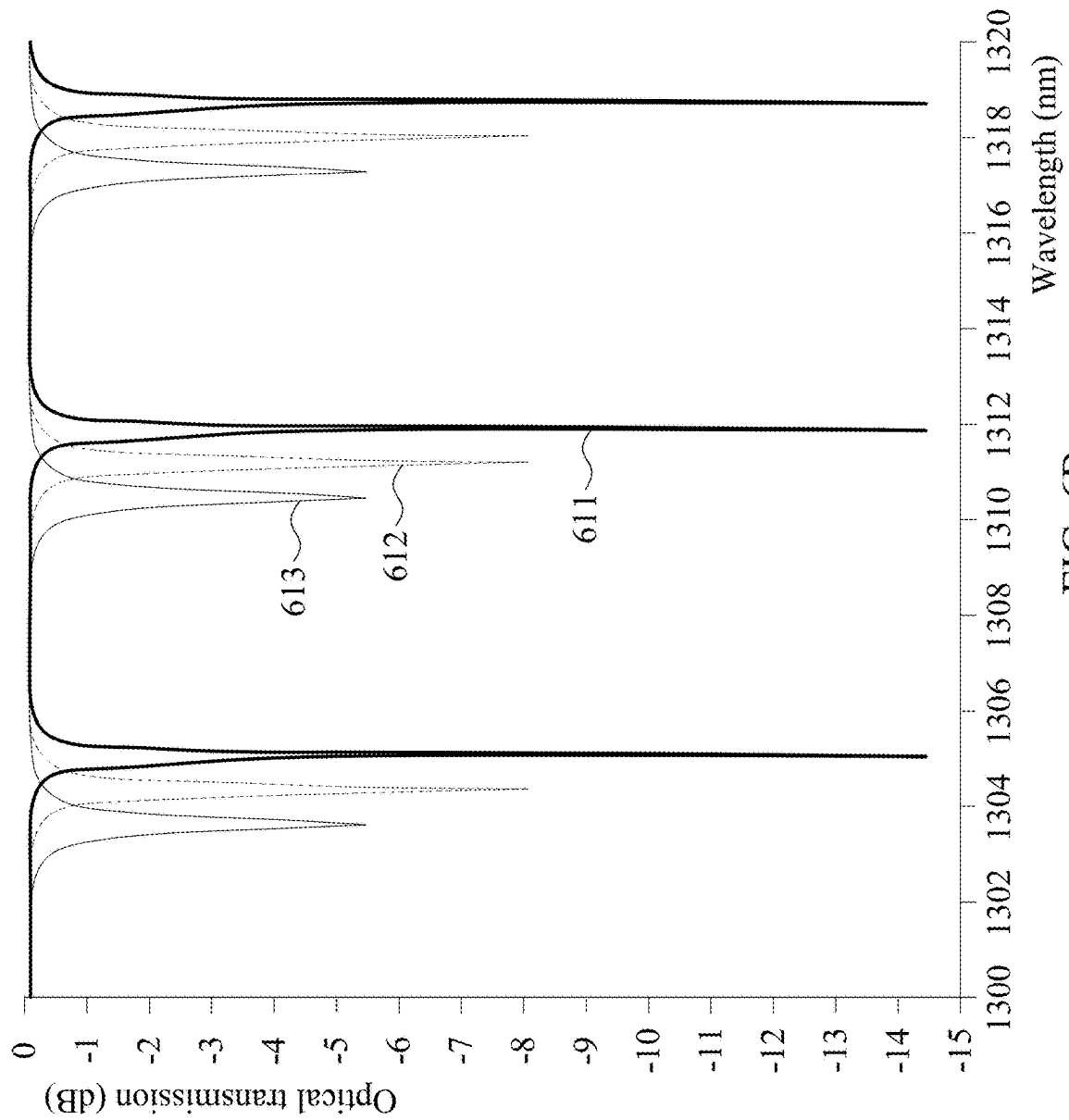


FIG. 6B

700

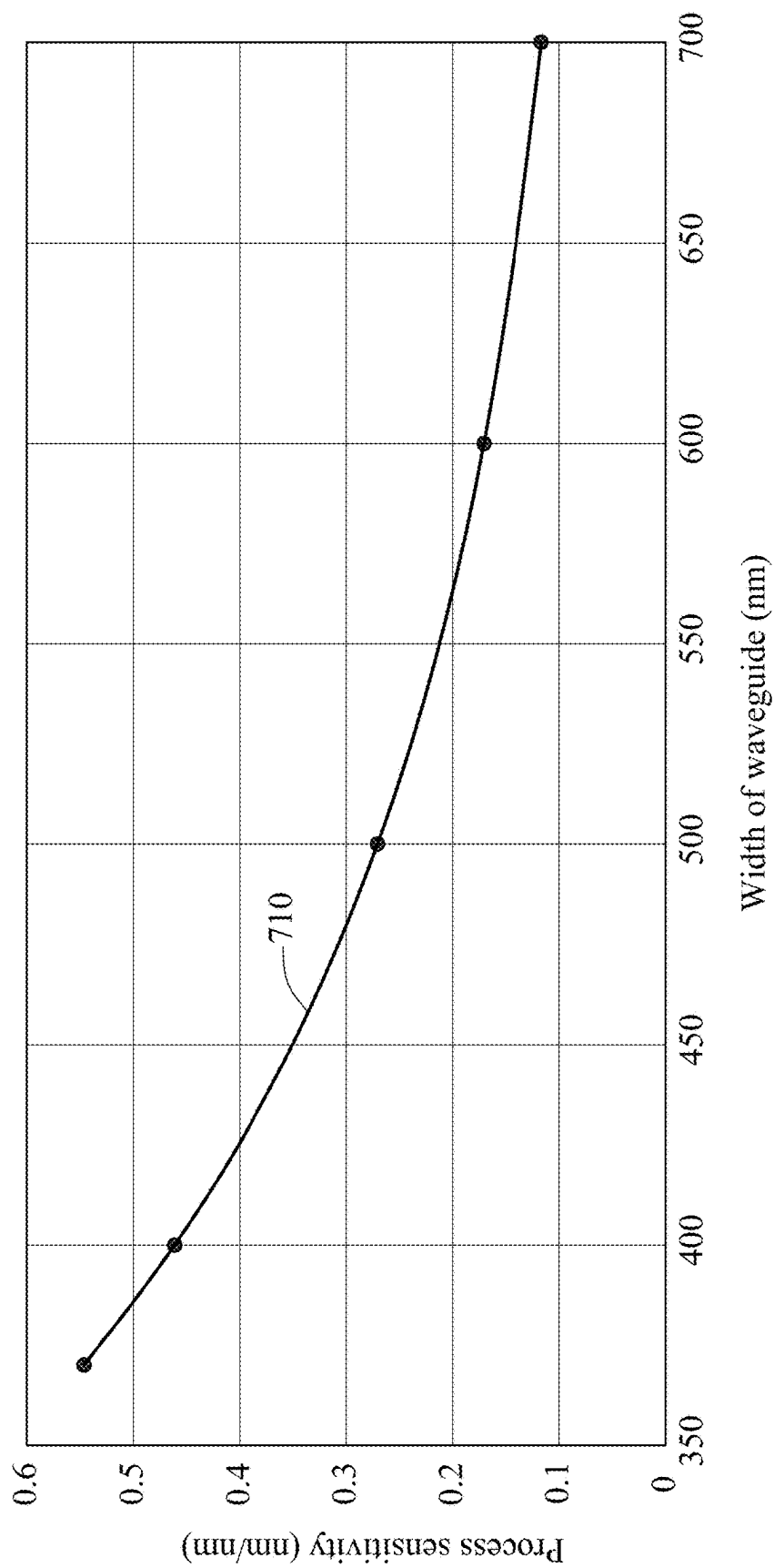


FIG. 7

800

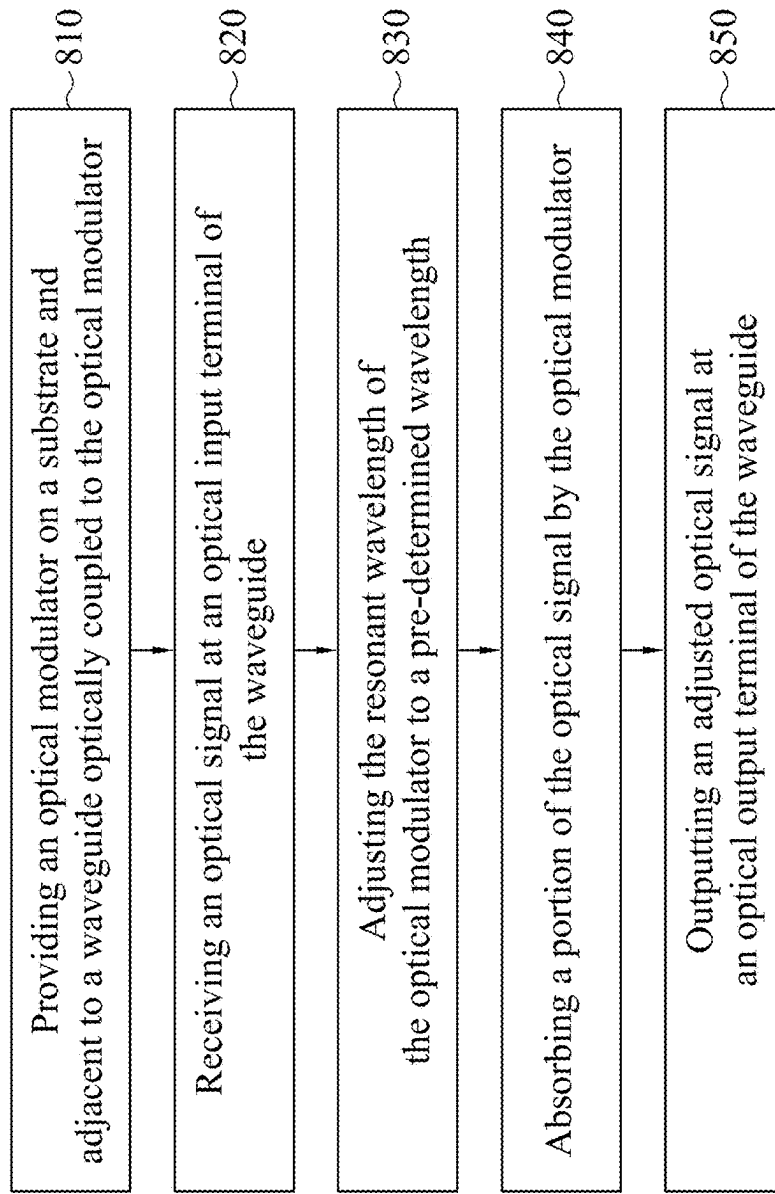


FIG. 8

**SEMICONDUCTOR DEVICE, PHOTONIC
CIRCUIT AND METHOD FOR ADJUSTING
RESONANT WAVELENGTH OF OPTICAL
MODULATOR**

**CROSS REFERENCE TO RELATED
APPLICATIONS**

[0001] This application is a continuation application of prior-filed U.S. application Ser. No. 18/599,189, filed Mar. 7, 2024, which is a continuation application of prior-filed U.S. application Ser. No. 17/674,646, filed Feb. 17, 2022, and claims the priority thereto.

BACKGROUND

[0002] Optical signaling and processing have become increasingly popular in recent years, particularly with the use of optical fiber-related applications for signal transmission. Accordingly, devices integrating optical components and electrical components are utilized in conversion of optical to electrical signals, and processing thereof. In the optical signaling field, optical modulators (for example, ring modulators or micro-ring modulators) are elements utilized for alleviation of process mismatch and calibration of the optical signals.

BRIEF DESCRIPTION OF THE DRAWINGS

[0003] Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is emphasized that, in accordance with standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

[0004] FIG. 1A is a block diagram of an optical communication system, in accordance with some embodiments.

[0005] FIG. 1B is a schematic diagram of a semiconductor structure of a photonic device, in accordance with some embodiments.

[0006] FIG. 2A is a top view of a photonic device, in accordance with some embodiments.

[0007] FIG. 2B is a cross-section of a photonic device along the section line A-A of FIG. 2A, in accordance with some embodiments.

[0008] FIG. 2C is a cross-section of a photonic device along the section line B-B of FIG. 2A, in accordance with some embodiments.

[0009] FIG. 2D is a cross-section of a photonic device along the section line C-C of FIG. 2A, in accordance with some embodiments.

[0010] FIG. 2E is a cross-section of a photonic device along the section line C-C of FIG. 2A, in accordance with some embodiments.

[0011] FIG. 3A is a top view of a photonic device, in accordance with some embodiments.

[0012] FIG. 3B is a cross-section of a photonic device along the section line B-B of FIG. 3A, in accordance with some embodiments.

[0013] FIG. 4A is a top view of a photonic device, in accordance with some embodiments.

[0014] FIG. 4B is a cross-section of a photonic device along the section line C-C of FIG. 4A, in accordance with some embodiments.

[0015] FIG. 5A is a top view of a photonic device, in accordance with some embodiments.

[0016] FIG. 5B is a cross-section of a photonic device along the section line C-C of FIG. 5A, in accordance with some embodiments.

[0017] FIG. 5C is a cross-section of a photonic device along the section line C-C of FIG. 5A, in accordance with some embodiments.

[0018] FIG. 6A is a graph illustrating optical transmission versus wavelength of the optical signal of an optical modulator, in accordance with some embodiments.

[0019] FIG. 6B is a graph illustrating optical transmission versus wavelength of the optical signal of an optical modulator, in accordance with some embodiments.

[0020] FIG. 7 is a graph illustrating process sensitivity versus width of the waveguide of an optical modulator, in accordance with some embodiments.

[0021] FIG. 8 is a flowchart showing a method for adjusting a resonant wavelength of an optical modulator, in accordance with some embodiments.

DETAILED DESCRIPTION

[0022] The following disclosure provides many different embodiments, or examples, for implementing different features of the provided subject matter. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

[0023] Further, spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature’s relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

[0024] Embodiments, or examples, illustrated in the drawings are disclosed as follows using specific language. It will nevertheless be understood that the embodiments and examples are not intended to be limiting. Any alterations or modifications in the disclosed embodiments, and any further applications of the principles disclosed in this document are contemplated as would normally occur to one of ordinary skill in the pertinent art.

[0025] Further, it is understood that several processing steps and/or features of a device may be only briefly described. Also, additional processing steps and/or features can be added, and certain of the following processing steps and/or features can be removed or changed while still implementing the claims. Thus, it is understood that the

following descriptions represent examples only, and are not intended to suggest that one or more steps or features are required.

[0026] In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

[0027] FIG. 1A is a block diagram of an optical communication system 10, in accordance with some embodiments. As shown in FIG. 1A, the optical communication system 10 includes an optical source 11, a modulator 12, a receiver 13, a driver 14, a processor 15 and waveguides 16. FIG. 1A also shows optical signals 17 transmitted within the optical communication system 10.

[0028] FIG. 1A illustrates how the optical source 11 may transmit a light signal to the modulator 12 with which the light signal 17 can be modulated and received by the receiver 13. The optical source 11, the modulator 12, and receiver 13 may be connected by the waveguides 16 (for example, optical fibers or optical conduits). In some embodiments, the optical source 11 may emit an optical signal 17. For example, the optical signal 17 can include laser beams and light beams. In some embodiments, the waveguides 16 may include optical fibers, optical waveguides, or optical conduits.

[0029] The optical communication system 10 may be part of the internal components of a computer system. For example, the processing system 10 may be part of, for example, a personal or laptop computer, with the modulator 12 included in a processor of the computer system and the receiver 13 included therein. The receiver 13 may be an internal card of the computer system, such as a video controller card, a network interface card, memory or the like. In one embodiment, the optical communication system 10 may be included in a single chip or chipset with the optical source 11 and the receiver 13 being internal components of the chip or chipset. In another embodiment, the optical communication system 11 may be included in a communications network with optical source 11 and receiver 13 being included in separate components of the communications network.

[0030] As will be discussed in further detail, the modulator 12 may include a waveguide disposed between p-type semiconductor materials and n-type semiconductor materials. In particular embodiments, these patterns may form discrete shapes from a light input end to a light output end of the waveguide. In one embodiment, the modulator 12 can be an optical modulator. For example, the modulator 12 can be a ring modulator (RM).

[0031] In some embodiments, the driver 14 is electrically connected to the processor 15. The driver can be configured to drive the modulator 12. In some embodiments, the optical source 11 may include a light source (e.g., a VCSEL diode). In some embodiments, the receiver 13 may include an amplifier and a photo detector (not shown in FIG. 1A). During optical communication between the optical source 11 and the receiver 13, the processor 15 may generate and transmit an electrical signal to the driver 14. Meanwhile, the driver 14 can control the modulator 12 based on the electrical signal generated by the processor 15, such that the optical signal 17 is emitted from the optical source 11 through the waveguide 16 to the modulator 12. In addition, the optical signal 17 irradiated onto the modulator 12 can be

modulated to generate an optical signal. The optical signal generated by the modulator 12 is transmitted to and received by the receiver 13 through the waveguide 16. Subsequently, the receiver 13 may convert the optical signal into a photo-current (another electrical signal) and the photo-current can be amplified by the amplifier. The amplified electrical signal can then be transmitted to other elements in the computer system.

[0032] FIG. 1B is a schematic diagram of a semiconductor structure 100 of a photonic device, in accordance with some embodiments. The semiconductor structure 100 can include a substrate 129, a dielectric layer 127, a semiconductor layer 128, a waveguide 126, a driver 14, and a modulator 12. In some embodiments, the modulator 12 can include optical coupling portion 123 and electrical coupling portions 121 and 122. FIG. 1B shows that the modulator 12 is coupled to the driver 14.

[0033] Referring to FIG. 1B, the semiconductor structure 100 includes the substrate 129. In some embodiments, the substrate 129 may be a silicon substrate, a silicon germanium substrate, or a substrate formed of other semiconductor materials. In some embodiments, the substrate 129 may be doped with p-type dopants (such as boron or BF₂), n-type dopants (such as phosphorus or arsenic), or a combination thereof. Alternatively, the substrate 129 may be an intrinsic semiconductor substrate. In alternative embodiments, the substrate 129 is a dielectric substrate formed of, for example, silicon oxide.

[0034] The dielectric layer 127 can be disposed on the substrate 129. In some embodiments, a material of the dielectric layer 127 includes silicon oxide, silicon nitride, titanium oxide, or the like. In some embodiments, the dielectric layer 127 can constitute multiple dielectric layers.

[0035] The semiconductor layer 128 can be disposed on the dielectric layer 127. That is, the semiconductor layer 128 can be disposed on the substrate 129. In some embodiments, the dielectric layer 127 can be disposed between the semiconductor layer 128 and the substrate 129. In some embodiments, a material of the semiconductor layer 128 may be the same or different from that of the substrate 129. For example, the semiconductor layer 128 may be made of a suitable elemental semiconductor, such as crystalline silicon, diamond, or germanium, a suitable compound semiconductor, such as gallium arsenide, silicon carbide, indium arsenide, or indium phosphide, or a suitable alloy semiconductor, such as silicon germanium carbide, gallium arsenic phosphide, or gallium indium phosphide. In some embodiments, the semiconductor layer 128 can include the modulator 12 and the waveguide 126. As shown in FIG. 1B, the semiconductor layer 128 can be doped to form various regions, for example, the electrical coupling portions 121 and 122.

[0036] In some embodiments, the waveguide 126 can be disposed on the substrate 129. The waveguide 126 can be formed in the semiconductor layer 128. The waveguide 126 can have an input terminal and an output terminal. The input terminal of the waveguide 126 may be coupled to the optical source 11 as shown in FIG. 1A. In some embodiments, the output terminal of the waveguide 126 can be coupled to the receiver 13 shown in FIG. 1A. The optical signal (for example, the optical signal 17 as shown in FIG. 1A) generated by the optical source 11 can be received at the input

terminal of the waveguide 126; transmitted through the waveguide 126; and then output at the output terminal of the waveguide 126.

[0037] The modulator 12 may include a waveguide. In some embodiments, the modulator 12 may include a curved waveguide. The modulator 12 can include the optical coupling portion 123 and the electrical coupling portions 121 and 122. In some embodiments, the modulator 12 may be disposed on the substrate 129 and adjacent to the waveguide 126. In some embodiments, the modulator 12 may be spaced apart from the waveguide 126 by a distance. The distance is small enough such that the optical signal in the waveguide 126 can be optically coupled to the modulator 12. In some embodiments, portions of the optical signal within a specific frequency/wavelength range in the waveguide 126 can be absorbed or refracted by the modulator 12, such that the optical signal can be modulated and output at the output terminal of the waveguide 126.

[0038] The optical coupling portion 123 of the modulator 12 can be annular or elliptical. In some embodiments, the optical coupling portion 123 can be spaced apart from the waveguide 126. In some embodiments, the optical coupling portion 123 can include a waveguide.

[0039] In some embodiments, the electrical coupling portions 121 and 122 may be formed in the semiconductor layer 128. The semiconductor layer 128 can be doped to form the electrical coupling portions 121 and 122. In some embodiments, the electrical coupling portions 121 and 122 are disposed on the substrate 129. The electrical coupling portions 121 and 122 can be disposed adjacent to the optical coupling portion 123. In some embodiments, the optical coupling portion 123 is disposed between the electrical coupling portions 121 and 122.

[0040] In some embodiments, the semiconductor material in the electrical coupling portion 121 may be doped with dopants of first conductivity type. Meanwhile, the semiconductor material in the electrical coupling portion 122 may be doped with dopants of second conductivity type. In some embodiments, the first conductivity type is opposite to the second conductivity type. For example, the dopants of first conductivity type may be p-type dopants and the dopants of the second conductivity type may be n-type dopants. That is, the semiconductor material in the electrical coupling portion 121 can be doped with p-type dopants while the semiconductor material in the electrical coupling portion 122 is doped with n-type dopants. Nevertheless, the electrical coupling portion 121 can also be n-type doped, and the electrical coupling portion 122 can be p-type doped. In some embodiments, the p-type dopants include, for example, boron, BF₂, or the like. On the other hand, the n-type dopants include, for example, phosphorus, arsenic, or the like.

[0041] Referring to FIG. 1B, the driver 14 can be electrically coupled to the modulator 12. The driver 14 can apply a voltage to the electrical coupling portion 121. In some embodiments, the driver 14 can apply a voltage to the electrical coupling portion 122. That is, the modulator 12 can be configured to receive the voltage through the electrical coupling portions 121 and 122. With the applied voltage, a resonant wavelength or frequency of the modulator 12 can be adjusted to approach a predetermined value. A part of the optical signal in the waveguide 126 can be optically coupled to the modulator when the wavelength of the part of the optical signal is resonant with the modulator

12. Accordingly, the desired output optical signal at the output terminal of the waveguide 126 can be modulated by absorbing a part of the optical signal by the modulator 12.

[0042] FIG. 2A is a top view of a photonic device, in accordance with some embodiments, including a modulator 12A and a waveguide 216. In some embodiments, the modulator 12A in FIG. 2A can correspond to the modulator 12 in FIG. 1B, and the waveguide 216 can correspond to the waveguide 126 in FIG. 1B. As shown in FIG. 2A, the modulator 12A can be spaced apart from the waveguide 216 by a distance 240. The distance 240 can be small enough to optically couple the optical signal in the waveguide 216 to the modulator 12A. The modulator 12A may include a waveguide (or optical coupling portion) 210, a low speed phase shifter portion 220, electrical coupling portions 211 and 212, and a heater 230. FIG. 2A includes section lines A-A, B-B, and C-C, while details of the cross-section along those section lines are presented in FIGS. 2B-2E.

[0043] Referring to FIG. 2A, the waveguide 216 can have an input terminal for receiving optical signal and an output terminal for transmitting the optical signal. In some embodiments, the waveguide 216 may be of a width W₂. In some embodiments, the width W₂ of the waveguide 216 may be in a range of 0.01 to 10 μm.

[0044] The modulator 12A includes at least an optical coupling portion (waveguide) 210. In some embodiments, the optical coupling portion 210 can be a curved waveguide. In some embodiments, the optical coupling portion 210 can be annular. In some embodiments, the waveguide 210 may be elliptical. The waveguide 210 may have a radius R₁. As R₁ increases, the free spectral range (FSR) of the modulator 12A can decrease. Therefore, the power for modulating the resonant of the modulator 12A can be reduced. In other words, the power consumption of the modulator 12A can be reduced as size of the modulator 12A increases.

[0045] In some embodiments, the waveguide 210 can be of a width W₁. For example, the width W₁ of the waveguide 210 may be in a range of 0.01 to 10 μm. In one embodiment, the width W₁ of the waveguide 210 may exceed 1 μm. In some embodiments, the width W₁ of the waveguide 210 may be in a range of 1 to 10 μm. The process sensitivity of the modulator 12A can decrease as the width W₁ increases. In other words, the stability of the modulator 12A may be improved as width W₁ increases.

[0046] The low speed phase shifter portion 220 in FIG. 2A can include electrical coupling portions 221 and 222, and optical coupling portion 223. In some embodiments, the optical coupling portion 223 is a part of the optical coupling portion 210, which may have different dopants doped therein. The electrical coupling portions 221 and 222 can be disposed adjacent to the optical coupling portion 223. In some embodiments, the optical coupling portion 223 is disposed between the electrical coupling portions 221 and 222.

[0047] In some embodiments, the semiconductor material in the electrical coupling portion 221 may be doped with dopants of a first conductivity type. The semiconductor material in the electrical coupling portion 222 may be doped with dopants of a second conductivity type. In some embodiments, the first conductivity type is different from the second conductivity type. For example, the dopants of first conductivity type may be p-type dopants, and the dopants of the second conductivity type may be n-type dopants. That is, the

electrical coupling portion **221** can be a p-doped portion while the electrical coupling portion **222** can be an n-doped portion.

[0048] In some embodiments, the semiconductor material in the optical coupling portion **223** can be undoped or an intrinsic semiconductor. Accordingly, the low speed phase shifter portion **220** can include a PIN junction. With the PIN junction, the resonant wavelength (frequency) of the modulator **12A** can be modulated. In some embodiments, the low speed phase shifter portion **220** can be the low speed PIN phase shifter (LSPIN) portion.

[0049] Referring to FIG. 2A, the modulator **12A** may include a heater **230** disposed thereon. In some embodiments, the modulator **12A** may include a dielectric layer (not shown in FIG. 2A) between the heater **230** and the optical coupling portion **210**. In some embodiments, under the heater **230**, electrical coupling portions **211** and **212**, and regions **210a** and **210b** of the optical coupling portion **210** are provided.

[0050] The optical coupling portion **210** may include two regions **210a** and **210b**. The region **210a** can be a part of the optical coupling portion **210**, which may have different dopants doped therein. In some embodiments, the region **210b** can be a part of the optical coupling portion **210**, which may have different dopants doped therein. In some embodiments, the electrical coupling portions **211** can be disposed adjacent to the region **210a**. That is, the region **210a** may be disposed between the electrical coupling portion **211** and the region **210b**. In some embodiments, the electrical coupling portion **210b** can be disposed adjacent to the region **210b**. That is, the region **210b** may be disposed between the electrical coupling portion **212** and the region **210a**.

[0051] In some embodiments, the semiconductor material in the region **210a** may be doped with dopants of a conductivity type. The semiconductor material in the region **210b** of the optical coupling portion **210** may be doped with dopants of a conductivity type, different from that of the region **210a** of the optical coupling portion **210**. For example, the semiconductor material in the region **210a** of the optical coupling portion **210** can be doped with p-type dopants while the semiconductor material in the region **210b** of the optical coupling portion **210** can be doped with n-type dopants.

[0052] The electrical coupling portions **211** and **212** are similar to the electrical coupling portions **221** and **222**, respectively. That is, the electrical coupling portion **211** can be a p-doped portion while the electrical coupling portion **212** can be an n-doped portion.

[0053] In some embodiments, the heater **230** is disposed on the electrical coupling portions **211** and **212** and the regions **210a** and **210b** of the optical coupling portion. With the heater **230**, the resonant wavelength (frequency) of the modulator **12A** can be modulated.

[0054] FIG. 2B is a cross-section of the photonic device along the section line A-A in FIG. 2A. FIG. 2B includes a substrate **219**, a dielectric layer **217**, regions **210a** and **210b** of the optical coupling portion, regions **211a**, **211b**, **212a**, and **212b** of the electrical coupling portion, a dielectric layer **235**, and a heater **230**.

[0055] As shown in FIG. 2B, the dielectric layer **217** is disposed on the substrate **219**. The substrate **219** is similar to the substrate **129** in FIG. 1B and the dielectric layer **217** is similar to the dielectric layer **127** in FIG. 1B, and thus detailed description thereof is omitted for brevity.

[0056] The optical coupling portion **210** can include two regions **210a** and **210b**. In one embodiment, the size of the region **210a** can differ from that of the region **210b**. In another embodiment, the size of the region **210a** can be identical to that of the region **210b**. For example, the width of the region **210a** can be substantially identical to that of the region **210b**. In some embodiments, the width of the region **210a** can exceed that of the region **210b**. The region **210a** can be disposed on the substrate **219**. In some embodiments, the dielectric layer **217** can be disposed between the region **210a** and the substrate **219**. The region **210b** can be disposed on the substrate **219** and adjacent to the region **210a**. In some embodiments, the dielectric layer **217** can be disposed between the region **210b** and the substrate **219**. In some embodiments, the regions **210a** and **210b** have a total width **W1**, which can correspond to the width **W1** in FIG. 2A.

[0057] Referring to FIG. 2B, a dielectric layer **235** is disposed on the regions **210a** and **210b** of the optical coupling portion, and the regions **211a**, **211b**, **212a**, and **212b** of the electrical coupling portions. In some embodiments, the property and material of the dielectric layer **235** may be similar to the dielectric layer **217**.

[0058] In some embodiments, the heater **230** can be disposed on the dielectric layer **235**. The heater **230** can be a metal heater. For example, the heater **230** can generate heat induced by electrical current. The form and type of the heater **230** is not limited. In some embodiments, the heater **230** can be configured to modulate the resonant wavelength of the modulator **12A** thermally. The heater **230** can provide heat to the modulator **12A**, so that the temperature thereof can be increased. In some embodiments, the modulator **12A** can have a temperature coefficient about $0.07 \text{ nm}^\circ/\text{C}$. For example, if the resonant wavelength of the modulator is 1312 nm at 27°C ., the thermally modulated resonant wavelength may be 1312.7 nm at 37°C . With the higher temperature, the resonant wavelength can be modulated at a nanometer level. In some embodiments, the resonant wavelength of the modulator **12A** can be increased thermally as the temperature increases.

[0059] The electrical coupling portion **211** in FIG. 2A may include two regions **211a** and **211b**. In some embodiments, the region **211a** can be disposed adjacent to the region **210a**. The region **211b** can be disposed adjacent to the region **211a** of the electrical coupling portion. In some embodiments, the region **211a** can be disposed between the region **211b** and the region **210a**. In one embodiment, the region **211b** can be of a height different from that of the region **211a**. For example, the height of the region **211b** can exceed the height of the region **211a**. The height of the regions of the electrical coupling portion **211** is not limited. For example, the height of the region **211b** may be substantially identical to the height of the region **211a**. In some embodiments, the region **211b** may be connected to the driver **14** (as shown in FIG. 1B).

[0060] In some embodiments, the semiconductor material of the regions **211a** and **211b** can be the same conductivity type. For example, the regions **211a** and **211b** can be both doped with p-type dopants. In one embodiment, the region **211a** can have a doping concentration identical to that of the region **211b**. In another embodiment, the doping concentration of the region **211a** can be different from that of the region **211b**. For example, the doping concentration of the region **211b** can exceed the doping concentration of the region **211a**. In some embodiments, the electrical coupling

portion **211** can include one or more regions. In other words, the electrical coupling portion **211** can include several regions having different doping concentration. In some embodiments, the doping concentration can decrease from the side of the electrical coupling portion **211** toward the optical coupling portion **210**. In some embodiments, the doping concentration can decrease gradually from the electrical coupling portion **211** toward the optical coupling portion **210**.

[0061] In some embodiments, the region **210a** can be doped with dopants the same as in the regions **211a** and **211b**. In other words, the region **210a** can be doped with p-type dopants. In some embodiments, the region **210a** can have a doping concentration less than the doping concentration of the region **211b**. In one embodiment, the region **210a** can have a doping concentration substantially identical to that of the region **211a**. In another embodiment, the doping concentration of the region **210a** can be different from that of the region **211a**. For example, the doping concentration of the region **210a** can be less than that of the region **211a**. The p-type doping concentration can decrease from the region **211b** toward the region **210a**.

[0062] The electrical coupling portion **212** in FIG. 2A may include two regions **212a** and **212b**. In some embodiments, the region **212a** can be disposed adjacent to the region **210b**. In some embodiments, the region **212a** can be disposed between the region **212b** and the region **210b**. In one embodiment, the region **212b** can be of a height different from that of the region **212a**. For example, the height of the region **212b** can exceed the height of the region **212a**. The height of the regions of the electrical coupling portion **212** is not limited. For example, the height of the region **212b** may be substantially identical to the height of the region **212a**. In some embodiments, the region **212b** may be connected to the driver **14** (as shown in FIG. 1B). With the region **211b** and the region **212b** connected to the driver **14**, the electrical signal can be transmitted through the region **211b**, **211a**, **210a**, **210b**, **212a**, and **212b**. That is, there can be a conductive path through the region **211b**, **211a**, **210a**, **210b**, **212a**, and **212b**.

[0063] In some embodiments, the semiconductor material of the regions **212a** and **212b** can be the same conductivity type. For example, the regions **212a** and **212b** can be both doped with n-type dopants. In one embodiment, the region **212a** can have a doping concentration identical to that of the region **212b**. In another embodiment, the doping concentration of the region **212a** can be different from that of the region **212b**. For example, the doping concentration of the region **212a** can exceed that of the region **212b**. In some embodiments, the electrical coupling portion **212** can include one or more regions. In other words, the electrical coupling portion **212** can include several regions having different doping concentrations. In some embodiments, the doping concentration can decrease from the side of the electrical coupling portion **212** toward the optical coupling portion **210**. In some embodiments, the doping concentration can decrease gradually from the electrical coupling portion **212** toward the optical coupling portion **210**.

[0064] In some embodiments, the region **210b** can be doped with dopants the same as in the regions **212a** and **212b**. In other words, the region **210b** can be doped with n-type dopants. In some embodiments, the region **210b** can have a doping concentration less than the doping concentration of the region **212b**. In one embodiment, the region

210b can have a doping concentration substantially identical to that of the region **212a**. In another embodiment, the doping concentration of the region **210b** can be different from that of the region **212a**. For example, the doping concentration of the region **210b** can be less than that of the region **212a**. The n-type doping concentration can decrease from the region **212b** toward the region **210b**.

[0065] The region **211a** and **211b** of the electrical coupling portion and the region **210a** of the optical coupling portion can be p-type doped at different concentrations, while the region **212a** and **212b** of the electrical coupling portion and the region **210b** of the optical coupling portion can be n-type doped at different concentrations. That is, the regions **211a**, **211b**, and **210a** and the regions **212a**, **212b**, and **210b** can form a P-N junction.

[0066] FIG. 2C is a cross-section of the photonic device along the section line B-B in FIG. 2A, which is included in the low speed phase shifter portion **220**. FIG. 2C includes a substrate **219**, a dielectric layer **217**, an optical coupling portion **223**, regions **211a**, **211b**, **211c**, **212a**, **212b**, and **212c** of the electrical coupling portion, and a dielectric layer **235**. Since the dielectric layer **217**, the substrate **219** and the dielectric layer **235** are substantially same as those in FIG. 2B, detailed description thereof is omitted for brevity.

[0067] The optical coupling portion **223** can be disposed on the substrate **219**. In some embodiments, the optical coupling portion **223** may be disposed between the substrate **219** and the dielectric layer **235**. The optical coupling portion **223** in FIG. 2C is the same as in FIG. 2A, and thus detailed description is omitted herefrom. In some embodiments, the optical coupling portion **223** is a part of the optical coupling portion **210**, which may have different dopants doped therein. That is, the width of the optical coupling portion **223** can be identical to that of the optical coupling portion **210** (i.e., the width **W1**).

[0068] The electrical coupling portion **221** in FIG. 2A may include three regions **221a**, **221b**, and **221c**. In some embodiments, the region **221a** can be disposed adjacent to the optical coupling portion **223**. The region **221b** can be disposed adjacent to the region **221a** of the electrical coupling portion. In some embodiments, the region **221a** can be disposed between the region **221b** and the optical coupling portion **223**. The region **221c** can be disposed adjacent to the region **221b** of the electrical coupling portion. In some embodiments, the region **221b** can be disposed between the region **221c** and the region **221a**.

[0069] In one embodiment, the region **221a** can be of a height identical to that of the region **221b**. In some embodiments, the region **221c** can be of a height different from that of the region **221b**. For example, the height of the region **221c** can exceed the height of the region **221b**. The height of the regions of the electrical coupling portion **221** is not limited. For example, the height of the region **221c** may be substantially identical to the height of the region **221b**. In some embodiments, the region **221c** may be connected to the driver **14** (as shown in FIG. 1B).

[0070] In some embodiments, the semiconductor material of the regions **221a**, **221b**, and **221c** can be the same conductivity type. For example, the regions **221a**, **221b**, and **221c** can be doped with p-type dopants. In one embodiment, the region **221a** can have a doping concentration identical to that of the region **221b**. In another embodiment, the doping concentration of the region **221a** can be different from that of the region **221b**. For example, the doping concentration of

the region **221b** can exceed the doping concentration of the region **221a**. In one embodiment, the region **221c** can have a doping concentration identical to that of the region **221b**. In another embodiment, the doping concentration of the region **221c** can be different from that of the region **221b**. For example, the doping concentration of the region **221c** can exceed the doping concentration of the region **221b**. In some embodiments, the electrical coupling portion **221** can include one or more regions. In other words, the electrical coupling portion **221** can include several regions having different doping concentrations. In some embodiments, the doping concentration can decrease from the side of the electrical coupling portion **221** toward the optical coupling portion **223**.

[0071] The electrical coupling portion **222** in FIG. 2A may include three regions **222a**, **222b**, and **222c**. In some embodiments, the region **222a** can be disposed adjacent to the optical coupling portion **223**. The region **222b** can be disposed adjacent to the region **222a** of the electrical coupling portion. In some embodiments, the region **222a** can be disposed between the region **222b** and the optical coupling portion **223**. The region **222c** can be disposed adjacent to the region **222b** of the electrical coupling portion. In some embodiments, the region **222b** can be disposed between the region **222c** and the region **222a**.

[0072] In one embodiment, the region **222a** can be of a height identical to that of the region **222b**. In some embodiments, the region **222c** can be of a height different from that of the region **222b**. For example, the height of the region **222c** can exceed the height of the region **222b**. The height of the regions of the electrical coupling portion **222** is not limited. For example, the height of the region **222c** may be substantially identical to the height of the region **222b**. In some embodiments, the region **222c** may be connected to the driver **14** (as shown in FIG. 1B).

[0073] The optical coupling portion **223** can be of a height identical to the regions **221c** and **222c**. In some embodiments, the height of the optical coupling portion **223** can be identical to that of the region **221a**. In some embodiments, the height of the optical coupling portion **223** can be identical to that of the region **221b**. In another embodiment, the height of the optical coupling portion **223** can be different from that of the region **221a** and **221b**. For example, the height of the optical coupling portion **223** can exceed that of the region **221a** and **221b**.

[0074] The optical coupling portion **223** can be of a width different from the width of the region **221a**, **221b**, **221c**, **222a**, **222b**, and **222c**. In one embodiment, the width of the optical coupling portion **223** can be less than the width of the region **221a**. In another embodiment, the width of the optical coupling portion **223** can exceed the width of the region **221a**. In some embodiments, the width of the optical coupling portion **223** can exceed a total width of the regions **221a**, **221b**, and **221c**. Similarly, the width of the optical coupling portion **223** can exceed a total width of the regions **222a**, **222b**, and **222c**.

[0075] In some embodiments, the semiconductor material of the regions **222a**, **222b**, and **222c** can be the same conductivity type. For example, the regions **222a**, **222b**, and **222c** can be doped with n-type dopants. In one embodiment, the region **222a** can have a doping concentration identical to that of the region **222b**. In another embodiment, the doping concentration of the region **222a** can be different from that of the region **222b**. For example, the doping concentration of

the region **222b** can exceed the doping concentration of the region **222a**. In one embodiment, the region **222c** can have a doping concentration identical to that of the region **222b**. In another embodiment, the doping concentration of the region **222c** can be different from that of the region **222b**. For example, the doping concentration of the region **222c** can exceed the doping concentration of the region **222b**. The electrical coupling portion **222** may include one or more regions. In some embodiments, the electrical coupling portion **222** can include several regions having different doping concentrations. In some embodiments, the doping concentration can decrease from the side of the electrical coupling portion **222** toward the optical coupling portion **223**.

[0076] With the region **221c** and the region **222c** connected to the driver **14**, the electrical signal can be transmitted through the regions **221c**, **221b**, **221a**, the optical coupling portion **223**, and the regions **222a**, **222b**, and **222c**. That is, there can be a conductive path through the regions **221c**, **221b**, **221a**, the optical coupling portion **223**, and the regions **222a**, **222b**, and **222c**.

[0077] In some embodiments, the semiconductor material in the optical coupling portion **223** can be undoped or an intrinsic semiconductor. The region **221a**, **221b**, and **221c** of the electrical coupling portion can be p-type doped at different concentrations, while the region **222a**, **222b**, and **222c** of the electrical coupling portion can be n-type doped at different concentrations. That is, the p-type regions **221a**, **221b**, and **221c**, the intrinsic (I) region **223**, and the n-type regions **222a**, **222b**, and **222c** can form a PIN junction. Accordingly, the low speed phase shifter portion **220** can include a PIN junction. With the PIN junction, the resonant wavelength (frequency) of the modulator **12A** can be modulated. In some embodiments, the resonant wavelength of the modulator **12A** can decrease with the higher voltage applied on such PIN junction. The modulator **12A** may be configured to receive a voltage through the region **221c**, **221b**, **221a**, the optical coupling portion **223**, and the regions **222a**, **222b**, and **222c** to decrease the resonant wavelength of the modulator **12A**.

[0078] In some embodiments, the p-type regions **221a**, **221b**, and **221c** may be symmetrical to the n-type regions **222a**, **222b**, and **222c** along the optical coupling portion **223**. In some embodiments, the size of the p-type regions **221a**, **221b**, and **221c** can be different from that of the n-type regions **222a**, **222b**, and **222c**. For example, the total width of the p-type regions **221a**, **221b**, and **221c** can exceed that of the n-type regions **222a**, **222b**, and **222c**.

[0079] FIG. 2D is a cross-section of a photonic device, in accordance with some embodiments. FIG. 2D shows the cross-section of the photonic device along the section line C-C in FIG. 2A. FIG. 2D includes a substrate **219**, a dielectric layer **217**, a semiconductor layer **218**, an optical coupling portion **210**, the waveguide **216**, and a dielectric layer **235**. Since the dielectric layer **217**, the substrate **219** and the dielectric layer **235** are substantially same as those in FIG. 2B, detailed description thereof is omitted for brevity.

[0080] The optical coupling portion **210** can be disposed on the substrate **219**. In some embodiments, the optical coupling portion **210** may be disposed between the substrate **219** and the dielectric layer **235**. The optical coupling portion **210** in FIG. 2D is the same as that of FIG. 2A, and thus detailed description is omitted herefrom. In some embodiments, the optical coupling portion **210** can be

formed in the semiconductor layer **218**. The semiconductor layer **218** in FIG. 2D is similar to the semiconductor layer **128** in FIG. 1B, and thus detailed description is omitted herefrom. In some embodiments, the optical coupling portion **210** can be of a width **W1** and a height **H1**. In some embodiments, the width **W1** can be in a range of 0.01 to 10 μm . In another embodiment, the width **W1** can exceed 1 μm . For example, the width **W1** can be in a range of 1 to 10 μm . In some embodiments, the height **H1** can exceed 0.01 μm . For example, the height **H1** can be in a range of 0.01 to 10 μm .

[0081] The waveguide **216** can be formed in the semiconductor layer **218**. In some embodiments, the waveguide **216** can be disposed on the substrate **219**. The waveguide **216** may be disposed between the substrate **219** and the dielectric layer **235**. The waveguide **216** in FIG. 2D is the same as that of FIG. 2A, and thus detailed description is omitted herefrom. The waveguide **216** can be of a width **W2**. In one embodiment, the width **W2** of the waveguide **216** can be different from the width **W1** of the optical coupling portion **210**. In another embodiment, the width **W2** can be identical to the width **W1**. In some embodiments, the width **W2** can be in a range of 0.01 to 10 μm . In some embodiments, the waveguide **216** can have a height substantially identical to that of the optical coupling portion **210**. In another embodiment, the height of the waveguide **216** can be different from that of the optical coupling portion **210**.

[0082] The waveguide **216** can be spaced apart from the optical coupling portion **210** by the distance **240** having a width **W3**. In one embodiment, the width **W3** can be identical to the width **W1**. In another embodiment, the width **W3** can be different from the width **W1**. For example, the width **W3** can be less than the width **W1**. In some embodiments, the width **W3** can be less than the width **W2**. In some embodiments, the width **W3** can be in a range of 0.01 to 10 μm .

[0083] In some embodiments, the waveguide **216** is disposed apart from the optical coupling portion with a gap of distance **240**. In some embodiments, the part of the semiconductor **218** under the gap can have a height **H2**. The height **H2** can be less than the height **H1**. In some embodiments, the height **H2** can be in a range of 0 to 10 μm . That is, there may be no semiconductor layer between the waveguide **216** and the optical coupling portion **210**.

[0084] The semiconductor layer **218** may have a structure similar to the electrical coupling portions **221** and **222**. In some embodiments, the semiconductor layer **218** can have a slab region having a width **W4** and a rib region having a width **W6** in left side of the optical coupling portion **210**. The slab region with width **W4** can have a height **H3**. In some embodiments, the width **W4** can be in a range of 0.01 to 10 μm . In some embodiments, the width **W6** can be in a range of 0 to 10 μm . That is, the rib region may be optional. In some embodiments, the height **H3** of the slab region can be in a range of 0 to 10 μm . That is, there may be no semiconductor layer adjacent to the left side of the optical coupling portion **210**.

[0085] Similarly, the semiconductor layer **218** can have a slab region having a width **W5** and a rib region having a width **W7** in right side of the optical coupling portion **210**. The slab region with width **W5** can also have a height substantially identical to the height **H3**. In some embodiments, the width **W5** can be in a range of 0.01 to 10 μm . In some embodiments, the width **W7** can be in a range of 0 to

10 μm . That is, the rib region may be optional. In some embodiments, since the height **H3** of the slab region can be in a range of 0 to 10 μm , there may be no semiconductor layer adjacent to the right side of the optical coupling portion **210**.

[0086] FIG. 2E is a cross-section of a photonic device, in accordance with some embodiments. FIG. 2E is a cross-section of the photonic device along the section line C-C in FIG. 2A.

[0087] Referring to FIG. 2E, the cross-section along the section line C-C is similar to that in FIG. 2D, differing therefrom in that in FIG. 2E, the semiconductor layer **218** may not include the rib region and the slab region beside the optical coupling portion **210** and the waveguide **216**. That is, the widths **W6** and **W7** can be zero and the height **H3** can be zero, and thus no rib regions and slab region would exist in the semiconductor layer **218**.

[0088] FIG. 3A is a top view of a photonic device, in accordance with some embodiments, in which the modulator **12B** is similar to the modulator **12A** in FIG. 2A, differing therefrom in that in FIG. 3A, the modulator **12B** can have a heater **330** covering a greater area of the modulator **12B**. The modulator **12B** can include a waveguide (or optical coupling portion) **310**, electrical coupling portions **321** and **322**, an optical coupling portion **323** and a heater **330**. FIG. 3A includes a section line B-B, while details of the cross-section along the section line B-B are presented in FIG. 3B.

[0089] In some embodiments, the heater **330** can cover a portion of the modulator **12B** from a top view perspective. In another embodiment, the heater **330** may cover all of modulator **12B**.

[0090] FIG. 3B is a cross-section of a photonic device, in accordance with some embodiments. FIG. 3B is a cross-section of the photonic device along the section line B-B in FIG. 3A.

[0091] Referring to FIG. 3B, the cross-section along the section line B-B is similar to that in FIG. 2C, differing therefrom in that in FIG. 3B, the heater **330** is disposed on the low speed phase shifter portion. FIG. 3B includes a substrate **319**, a dielectric layer **317**, an optical coupling portion **323**, regions **321a**, **321b**, and **321c** of the electrical coupling portion **321**, the regions **322a**, **322b**, and **322c** of the electrical coupling portion **322**, a dielectric layer **335**, and the heater **330**. Since the dielectric layer **317**, the substrate **319**, the regions **321a**, **321b**, and **321c** of the electrical coupling portion **321**, the optical coupling portion **323**, the regions **322a**, **322b**, and **322c** of the electrical coupling portion **322**, and the dielectric layer **335** are substantially same as the dielectric layer **217**, the substrate **219**, the regions **221a**, **221b**, and **221c** of the electrical coupling portion **221**, the optical coupling portion **223**, the regions **222a**, **222b**, and **222c** of the electrical coupling portion **222**, and the dielectric layer **235** in FIG. 2C, detailed description thereof is omitted for brevity.

[0092] As shown in FIG. 3B, the heater **330** can be disposed on the regions **321a**, **321b**, and **321c** of the electrical coupling portion **321**, the optical coupling portion **323**, and the regions **322a**, **322b**, and **322c** of the electrical coupling portion **322**. Therefore, the heater **330** and the low speed phase shifter can be configured to receive electrical signal or voltage to modulate the resonant wavelength of the modulator **12B**.

[0093] FIG. 4A is a top view of a photonic device, in accordance with some embodiments, in which the modulator

12C is similar to the modulator 12A in FIG. 2A, differing therefrom in that in FIG. 4A, the modulator 12C can have heaters 430a and 430b covering different portions of the modulator 12C. The modulator 12C can include a waveguide (or optical coupling portion) 410, and heaters 430a and 430b. FIG. 4A includes a section line C-C, while details of the cross-section along the section line C-C are presented in FIG. 4B.

[0094] In some embodiments, the heater 430a can be identical to the heater 230 in FIG. 2A. In some embodiments, the heater 430b can cover a portion of the modulator 12C different from the portion covered by the heater 430a from the top view perspective. In one embodiment, the heater 430a can overlap with the heater 430b. In another embodiment, the heater 430b can be spaced apart from the heater 430a. For example, the heater 430b can cover the part of the optical coupling portion 410 that may not doped with any dopants. In some embodiments, the heater 430b can cover a part of the waveguide 416.

[0095] FIG. 4B is a cross-section of the photonic device along the section line C-C in FIG. 4A, similar to that in FIG. 2D, differing therefrom in that in FIG. 4B, the heater 430b is disposed on the waveguide 416 and the optical coupling portion 410. FIG. 4B includes a substrate 419, a dielectric layer 417, a semiconductor layer 418, an optical coupling portion 410, the waveguide 416, a dielectric layer 435, and the heater 430b. Since the dielectric layer 417, the substrate 419, the semiconductor layer 418, the optical coupling portion 410, the waveguide 416, and the dielectric layer 435 are substantially same as the dielectric layer 217, the substrate 219, the semiconductor 218, the optical coupling portion 210, the waveguide 216, and the dielectric layer 235 in FIG. 2D, detailed description thereof is omitted for brevity.

[0096] As shown in FIG. 4B, the heater 430b can be disposed on the optical coupling portion 410 and the waveguide 416. The waveguide 416 can be spaced apart from the optical coupling portion 410 in a distance 440. The different arrangement of the heater can provide flexible modulator design according to needs.

[0097] Referring to FIG. 5A, the modulator 12D is similar to the modulator 12A in FIG. 2A, differing therefrom in that in FIG. 5A, the waveguide 516 may be curved. The modulator 12D can include a waveguide (or optical coupling portion) 510, and the waveguide 516 disposed apart from the waveguide 510 by a distance 540. FIG. 5A includes a section line C-C, while details of the cross-section along the section line C-C are presented in FIG. 5B.

[0098] In some embodiments, the waveguide 516 may be concave with respect to the waveguide 510. Therefore, the waveguide 516 may have a curvature substantially conforming to a portion of the waveguide 510. In that case, the optical coupling area between the waveguide 510 and the waveguide 516 may be increased. Accordingly, the stability of the modulator 12D can be improved.

[0099] FIG. 5B is a cross-section of the photonic device along the section line C-C in FIG. 5A, substantially identical to that in FIG. 2D, although the waveguide 516 is curved in the top view perspective.

[0100] FIG. 5C is a cross-section of the photonic device along the section line C-C in FIG. 5A, substantially identical to that in FIG. 2E, although the waveguide 516 is curved in the top view perspective.

[0101] FIG. 6A is a graph illustrating optical transmission versus wavelength of the optical signal of an optical modu-

lator, in accordance with some embodiments. FIG. 6A shows the shift of the resonant wavelength of the optical modulator with respect to temperature. Referring to FIG. 6A, the x-axis represents the wavelength (nm) of the optical signal coupled to the optical modulator. The y-axis represents the optical transmission (dB) of the optical signal. The line 601 represents resonance at a temperature of 300K, and line 602 represents resonance at a temperature of 310K, and the line 603 represents resonance at a temperature of 320K.

[0102] According to the line 601, the modulator may have resonant wavelength about 1305 and 1312 nm, at which the peaks occur. According to the line 602, the modulator may have resonant wavelength of about 1306 and 1312.5 nm, at which the peaks occur. According to the line 603, the modulator may have resonant wavelength of about 1307.2, and 1314.1 nm, at which the peaks occur. Referring to FIG. 6A, the resonant wavelength of the modulator can be modulated to be increased with higher temperature.

[0103] FIG. 6B is a graph illustrating optical transmission versus wavelength of the optical signal of an optical modulator, in accordance with some embodiments. FIG. 6B shows the shift of the resonant wavelength of the optical modulator with respect to the voltage applied on the low speed phase shifter in the modulator. In some embodiments, the low speed phase shifter can be a low speed PIN phase shifter (LSPIN). Referring to FIG. 6B, the x-axis represents the wavelength (nm) of the optical signal coupled to the optical modulator. The y-axis represents the optical transmission (dB) of the optical signal. The line 611 represents resonance when the LSPIN is configured to receive a voltage of 0V; the line 612 represents resonance when the LSPIN is configured to receive a voltage of 1V, and the line 613 represents resonance when the LSPIN is configured to receive a voltage of 2V.

[0104] According to the line 611, the modulator may have resonant wavelength of about 1305, 1312, and 1319 nm, at which the peaks occur. According to the line 612, the modulator may have resonant wavelength of about 1304.2, 1311, and 1318 nm, at which the peaks occur. According to the line 613, the modulator may have resonant wavelength of about 1303.2, 1310.2, and 1317.1 nm, at which the peaks occur. Referring to FIG. 6B, the resonant wavelength of the modulator can be modulated to be increased as increased voltage is applied on the LSPIN.

[0105] FIG. 7 is a graph illustrating process sensitivity versus width of the waveguide of an optical modulator, in accordance with some embodiments. Referring to FIG. 7, the x-axis represents the width (nm) of the waveguide of the optical modulator. The y-axis represents the process sensitivity (nm/nm) of the optical signal. The width of the waveguide can be the width W1 of the waveguide 210 as shown in FIG. 2A. The line 710 shows that the optical modulator process sensitivity improves with increased width of the waveguide of the optical modulator.

[0106] In some embodiments, when the width of the waveguide is 400 nm, the process sensitivity is about 0.46 nm/nm. When the width of the waveguide is 600 nm, the process sensitivity is about 0.18 nm/nm. Accordingly, at width of the waveguide of 600 nm, the modulator is less sensitive, and thus more stable.

[0107] FIG. 8 is a flowchart 800 showing a method for adjusting a resonant wavelength of an optical modulator, in accordance with some embodiments of the present disclosure. In some embodiments, this method can be conducted

by a semiconductor device. In some embodiments, this method can be conducted by a photonic circuit. In some embodiments, the method can be performed by the modulator shown in FIGS. 1B, 2A-2E, 3A-3B, 4A-4B, and 5A-5B.

[0108] In operation **810**, the optical modulator is provided on a substrate and adjacent to a waveguide optically coupled to the optical modulator. In some embodiments, the waveguide includes an optical input terminal and an optical output terminal.

[0109] In operation **820**, an optical signal can be received at the optical input terminal of the waveguide. In some embodiments, the optical signal can be transmitted through the waveguide.

[0110] In operation **830**, the resonant wavelength of the optical modulator can be adjusted to a predetermined wavelength. The predetermined waveguide can be determined by the needs.

[0111] In operation **840**, a portion of the optical signal can be absorbed by the optical modulator. When the wavelength of the portion of the optical signal corresponds to the resonant wavelength of the optical modulator, the portion of the optical signal can be optically coupled to the optical modulator.

[0112] In operation **850**, an adjusted optical signal can be output at the optical output terminal of the waveguide. Since a portion of the optical signal is optically coupled to the optical modulator, the adjusted optical signal would lack such portion of optical signal. Therefore, the adjusted optical signal can be adjusted to be the desired signal (light) output at the optical output terminal of the waveguide.

[0113] According to some embodiments, a semiconductor device is provided. The semiconductor device includes a substrate, a first waveguide disposed on the substrate, and a second waveguide disposed on the substrate and spaced apart from the first waveguide with a first distance. In addition, the second waveguide includes a first electrical coupling portion having a first type doping, a second electrical coupling portion having a second type doping, and an optical coupling portion disposed between the first electrical coupling portion and the second electrical coupling portion, wherein the second waveguide is configured to receive a first voltage through the first electrical coupling portion and the second electrical coupling portion to decrease a resonant wavelength of the second waveguide.

[0114] According to other embodiments, a photonic circuit is provided. The photonic circuit includes a substrate, a first waveguide disposed on the substrate, and a second waveguide disposed on the substrate and separated apart from the first waveguide. In addition, the second waveguide includes an optical coupling portion, a first electrical coupling portion adjacent to the optical coupling region and having a first type doping, a second electrical coupling portion adjacent to the optical coupling region and having a second type doping. Wherein the optical coupling portion has a doping concentration less than that of the first electrical coupling portion and the second electrical coupling portion, and wherein the first electrical coupling portion of the second waveguide is configured to receive a first voltage to decrease a resonant wavelength of the second waveguide in nanometer level.

[0115] According to other embodiments, a method for adjusting a resonant wavelength of an optical modulator. The method includes providing the optical modulator on a substrate and adjacent to a waveguide optically coupled to

the optical modulator, wherein the waveguide includes an optical input terminal and an optical output terminal; receiving an optical signal at the optical input terminal of the waveguide; adjusting the resonant wavelength of the optical modulator to a predetermined wavelength; absorbing a portion of the optical signal by the optical modulator; and outputting an adjusted optical signal at the optical output terminal of the waveguide.

[0116] The methods and features of the present disclosure have been sufficiently described in the above examples and descriptions. It should be understood that any modifications or changes without departing from the spirit of the present disclosure are intended to be covered in the protection scope of the present disclosure.

[0117] Moreover, the scope of the present application is not intended to be limited to the particular embodiments of the process, machine, manufacture, and composition of matter, means, methods and steps described in the specification. As those skilled in the art will readily appreciate from the present disclosure, processes, machines, manufacture, composition of matter, means, methods or steps presently existing or later to be developed, that perform substantially the same function or achieve substantially the same result as the corresponding embodiments described herein, may be utilized according to the present disclosure.

[0118] Accordingly, the appended claims are intended to include within their scope: processes, machines, manufacture, compositions of matter, means, methods or steps. In addition, each claim constitutes a separate embodiment, and the combination of various claims and embodiments are within the scope of the present disclosure.

What is claimed is:

1. A semiconductor device, comprising:
a substrate; and
an optical modulator disposed on the substrate, the optical modulator including a first PIN portion and a second PIN portion apart from the first PIN portion,
wherein the optical modulator is configured to receive a voltage from a driver to decrease a resonant wavelength of the optical modulator.
2. The semiconductor device of claim 1, further comprising:
a dielectric layer disposed on the optical modulator; and
a heater disposed on the dielectric layer.
3. The semiconductor device of claim 2, wherein the heater is configured to increase the resonant wavelength of the optical modulator thermally.
4. The semiconductor device of claim 2, wherein the heater covers the first PIN portion of the optical modulator from a top view perspective.
5. The semiconductor device of claim 1, wherein the optical modulator is elliptical.
6. The semiconductor device of claim 1, further comprising a curved waveguide disposed on the substrate and spaced apart from the optical modulator, wherein a first curvature of the curved waveguide is substantially conformed to a second curvature of an optical coupling portion of the optical modulator.
7. The semiconductor device of claim 6, wherein the optical coupling portion of the optical modulator connects the first PIN portion and the second PIN portion, wherein the optical coupling portion has a width in a range of 0.01 to 10 μm .

8. The semiconductor device of claim **1**, wherein the first PIN portion includes a first electrical coupling portion having a first type doping, a second electrical coupling portion having a second type doping, and an undoped portion between the first electrical coupling portion and the second electrical coupling portion, wherein a doping concentration of the first electrical coupling portion decrease gradually toward the undoped portion, and wherein a doping concentration of the second electrical coupling portion decrease gradually toward the undoped portion.

9. The semiconductor device of claim **8**, wherein the first electrical coupling portion includes a first region connected to the driver and a second region connecting the first region and the undoped portion, wherein a height of the first region is greater than a height of the second region.

10. The semiconductor device of claim **8**, wherein the second electrical coupling portion includes a third region connected to the driver and a fourth region connecting the third region and the undoped portion, wherein a height of the third region is greater than a height of the fourth region.

11. The semiconductor device of claim **9**, wherein a height of the undoped portion is greater than the height of the second region.

12. A photonic circuit, comprising:

a waveguide; and

a ring modulator separated apart from the waveguide, the ring modulator including an optical coupling portion and a low speed PIN phase shifter (LSPIN) portion, wherein the LSPIN portion of the ring modulator is configured to receive a voltage to decrease a resonant wavelength of the ring modulator in nanometer level.

13. The photonic circuit of claim **12**, further comprising a first heater disposed on the ring modulator and covering a portion of the ring modulator from a top view perspective.

14. The photonic circuit of claim **13**, further comprising a second heater disposed on the ring modulator and apart

from the first heater, wherein the second heater covers another portion of the ring modulator from a top view perspective.

15. The photonic circuit of claim **12**, wherein the ring modulator is elliptical.

16. The photonic circuit of claim **12**, wherein the waveguide is curved, and a first curvature of the waveguide is substantially conformed to a second curvature of a part of the optical coupling portion of the ring modulator.

17. A photonic circuit, comprising:

an optical modulator including an optical coupling portion and a low speed phase shifter portion,

a first heater disposed on the optical modulator,

wherein the optical modulator is configured to receive a voltage through the low speed phase shifter portion to decrease a resonant wavelength of the optical modulator, and wherein the first heater is configured to increase the resonant wavelength of the optical modulator thermally.

18. The photonic circuit of claim **17**, wherein the low speed phase shifter portion includes a first electrical coupling region having a first type doping, a second electrical coupling region having a second type doping, and an third region between the first electrical coupling region and the second electrical coupling region, wherein the third region is connected to the optical coupling portion to carry optical signals, wherein a doping concentration of the third region less than that of the first electrical coupling region and the second electrical coupling region.

19. The photonic circuit of claim **17**, further comprising a second heater disposed on the optical modulator and spaced apart from the first heater, wherein the second heater covers another portion of the optical modulator from a top view perspective.

20. The photonic circuit of claim **17**, wherein the low speed phase shifter portion is free of coverage of the first heater.

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